MASTR PROGRESS LINE

CUSTOM EXECUTIVE

MAINTENANCE MANUAL



150.8-174 MHz

TWO-WAY FM MOBILE COMBINATIONS

LBI-4343A

GENERAL ELECTRIC

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---WARNING--

No one should be permitted to handle any portion of the equipment that is supplied with voltage or RF power; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

EQUIPMENT INDEX

EQUIPMENT	MODEL OR TYPE NUMBER		
FM TRANSMITTER	KT-25-A		
FM RECEIVER	ER-48-C		
CHANNEL GUARD BOARD	4EK14B11		
POWER CABLE	19A129305G1		
MOUNTING HARDWARE	19A129302G1		
CONTROLLED RELUCTANCE MICROPHONE	4EM25L10		
Microphone Bracket	7141414G2		
ALIGNMENT TOOLS	<u> </u>		
Hex Slug Type	4038831P1		
Slotted Screw Type	4033530G2		
150.8-174 MHz ANTENNA	4EY12A13		

OPTIONAL EQUIPMENT

10-WATT SPEAKER (Option 8427)	4EZ18A14
CHANNEL GUARD HOOKSWITCH (Option 8428)	19C303571G4
ALTERNATOR FILTER (Option 8426)	19C320174G1
GUTTER-MOUNT ANTENNA (Option 5982)	4EY20A10

SPECIFICATIONS*

GENERAL

150.8-174 MHz FREQUENCY RANGE

3-3/8" x 8-3/8" x 13-1/4" DIMENSIONS (H x W x D)

WEIGHT (less accessories) 15 pounds

BATTERY DRAIN

Receiver (at 13.8 VDC)

Standby (squelched) 120 milliamps Standby (unsquelched) 400 milliamps

Transmitter

Transmit (at 13.8 VDC) 5.5 amperes

 -30° C to $+60^{\circ}$ C (-22° F to 140° F) OPERABLE TEMPERATURE RANGE

Transmit: 20% DUTY CAPABILITY

Receive: Continuous

MAXIMUM FREQUENCY SPACING 0.4%

TRANSMITTER

POWER OUTPUT 20 Watts

 $\pm .0005\%$ (-30°C to +60°C, 25°C reference) FREQUENCY STABILITY

SPURIOUS AND HARMONIC

At least 56 dB below rated power output RADIATION

MODULATION Adjustable from 0 to ±5 kHz swing with

instantaneous modu-

lation limiting

AUDIO FREQUENCY Within +1 and -3 dB of a 6 dB/octave pre-emphasis from 300 to

3000 Hz per EIA standards

DISTORTION Less than 5% @ 1 kHz DEVIATION SYMMETRY

0.6 kHz maximum (narrow band)

CRYSTAL MULTIPLICATION FACTOR

24

RECEIVER

AUDIO OUTPUT 1.5 Watts at less than 10% distortion

SENSITIVITY

12-dB SINAD (EIA Method) 0.3 μν

20-dB Quieting Method 0.4 μν

SELECTIVITY

EIA Two-Signal Method -40 dB (adjacent channel, 30 kHz channels)

20-dB Quieting Method -100 dB at ±20 kHz

SPURIOUS RESPONSE -90 dB

FIRST OSCILLATOR STABILITY $\pm .001\%$ (-30°C to +60°C, 25°C reference)

±7 kHz INTERMODULATION -70 dB

FREQUENCY RESPONSE +1 and -8 dB of a standard 6-dB per octave de-emphasis curve from 300 to 3000 Hz

SQUELCH SENSITIVITY

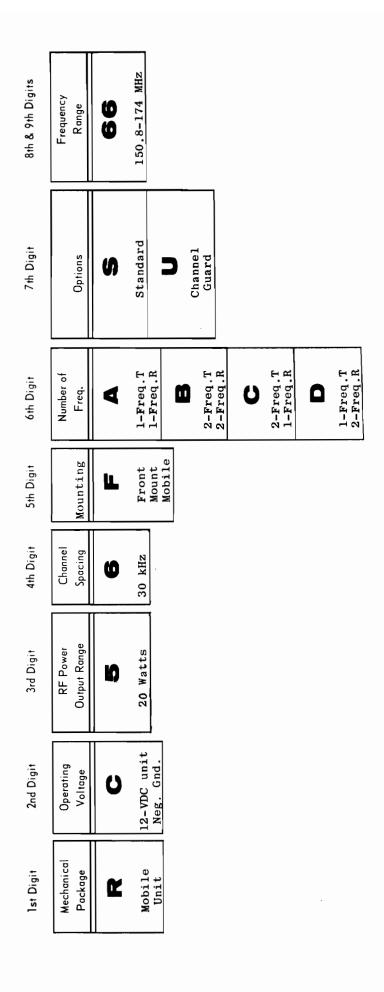
MODULATION ACCEPTANCE

4 dB SINAD (0.1 μv typical) Critical Squelch

Maximum Squelch Greater than 20 dB quieting

^{*} These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

COMBINATION NOMENCLATURE



DESCRIPTION

MASTR Progress Line Custom Executive mobile radio combinations are highly reliable, ruggedly constructed units that are designed to meet the most stringent requirements in the field of two-way radios. The radios are fully transistorized - using silicon transistors for added reliability. Since no tubes are used, the radio is ready to transmit at full power the instant the power is turned on.

No high-voltage power supply is required as the highest voltage in the radio is supplied by the vehicle battery.

Centralized metering jacks for the transmitter and receiver permit simplified alignment and troubleshooting.

TRANSMITTER

The transmitter consists of a transistorized exciter and power amplifier board. The standard transmitter may be equipped with:

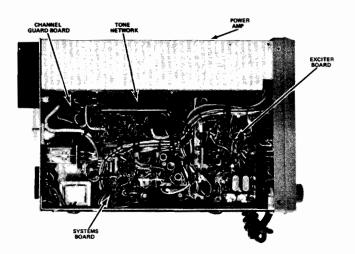
- One or two frequencies
- Channel Guard (tone squelch)

RECEIVER

The fully transistorized receiver is mounted on a single printed wiring board for increased reliability. A copper-plated housing and metal cover that completely encloses the receiver provides excellent shielding. The standard receiver may be equipped with:

- One or two frequencies
- Channel Guard (tone squelch)

TOP VIEW



CONTROL UNIT

The control unit is attached to the front of the two-way radio. The control panel contains all operating controls and a loudspeaker.

INITIAL ADJUSTMENT

After the two-way radio has been installed (as described in the INSTALLATION Manual), the following adjustments should be made by an electronics technician who holds a lst or 2nd Class FCC Radiotelephone license. Alignment tools are provided with the radio.

Make sure that a RADIO TRANSMITTER IDENTIFICATION form (FCC Form 452-C or General Electric Form ECP-82) has been filled out and attached to the transmitter.

TRANSMITTER ADJUSTMENT

The initial adjustment for the transmitter includes loading the power amplifier into the antenna, and checking the frequency and modulation. For the Initial Adjustment procedure, refer to the transmitter ALIGN-MENT PROCEDURE (See Table of Contents).

RECEIVER ADJUSTMENT

The initial adjustment for the reciever includes zeroing the receiver to the system operating frequency, and matching the antenna transformer to the antenna. For the initial adjustment procedure, refer to the FRONT END ALIGNMENT PROCEDURE (See Table of Contents).

BOTTOM VIEW

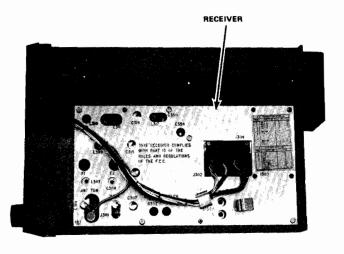


Figure 1 - Module Layout

OPERATION

Complete operating instructions for the Two-Way Radio are provided in the separate OPERATOR'S MANUAL. The basic procedures for receiving and transmitting messages follows:

TO RECEIVE A MESSAGE

- Turn the radio on by turning the OFF-VOLUME control halfway to the right.
- 2. Place the MONITOR-SQUELCH button in the MONITOR position and adjust the VOLUME control for a comfortable listening level. Then place the switch in the SQUELCH position.

The radio is now ready to receive messages from other radios in the system.

TO TRANSMIT A MESSAGE

- Apply power to the transmitter by turning the OFF-VOLUME control to the ON position.
- 2. Press the push-to-talk button on the microphone and speak across the face of the microphone in a normal (or softer) voice. Release the button as soon as the message has been given. The red signal light on the control panel will glow each time the microphone button is pressed, indicating that the transmitter is keyed.

MAINTENANCE

PREVENTIVE MAINTENANCE

To insure high operating efficiency and to prevent mechanical and electrical failures from interrupting system operations, routine checks should be made of all mechanical and electrical parts at regular intervals. This preventive maintenance should include the maintenance checks listed in the following table.

TEST AND TROUBLESHOOTING PROCEDURES

Whenever difficult servicing problems

occur, the test procedure for transmitter and receiver can be used by the serviceman to compare the actual performance of the unit against the specifications met by the unit when shipped from the factory. The test procedures are located on the back of the applicable alignment procedure.

In addition, specific troubleshooting procedures are available for the transmitter and receiver (refer to the Table of Contents). For best results, the test procedures should be used in conjunction with the troubleshooting procedures.

DISASSEMBLY

To gain access to the transmitter or receiver for servicing, remove the 4 screws on each side of the radio. Then lift off the top cover, and slide off the bottom cover.

To remove the PA Assembly for servicing:

- Remove the 8 screws in the PA cover.
- 2. Remove the uncolored screws holding the receiver to the chassis and lift out the receiver.
- 3. Remove the 4 flat-head screws holding the control unit to the chassis.
- 4. Remove the 2 screws holding the cover mounting bracket.
- Remove the mounting bracket screws for the PA feed-through capacitors and move it out of the way.
- 6. Remove the 5 mounting screws in the bottom of the PA Assembly and lift out the board.

-note -

Before reassembling the PA, make sure there is an adequate amount of silicon grease between the PA heatsink and the chassis.

	I	NTERVAL
MAINTENANCE CHECKS	6 Months	As Required
CONNECTIONS - Check power and ground connections periodically for tightness. Loose or poor connections to the power source will cause excessive voltage drops and faulty operation.	х	
ELECTRICAL SYSTEM - Check the voltage regulator and alternator or generator periodically to keep the electrical system within safe and economical operating limits. If the alternator or generator voltage is excessive, indicator lights, etc., may burn out periodically. This condition is indicated when the battery loses water rapidly. Usage of 1 or 2 ounces of water per cell per week is acceptable for batteries in continuous operation.		х
MECHANICAL INSPECTION - Since mobile units are subject to constant shock and vibration, check for loose plugs, nuts, screws, and parts to make sure that nothing is working loose.	х	
ANTENNA - Keep the antenna, antenna base and all contacts clean and free from dirt or corrosion. If the antenna or its base should become coated or poorly grounded, loss of radiation and a weak signal will result.	х	
ALIGNMENT - Check the transmitter and receiver meter readings periodically, and "touch-up" the alignment when necessary. Refer to the applicable ALIGNMENT PROCEDURE and Troubleshooting Sheet for typical voltage readings.		х
FREQUENCY CHECK - Check transmitter frequency and deviation as required by FCC. Normally, these checks are made when the unit is first put into operation, after the first six months, and once a year thereafter.		х

CIRCUIT ANALYSIS

TRANSMITTER

Transmitter Type KT-25-A is a crystal controlled, frequency modulated transmitter designed for one- or two-frequency operation in the 150.8 to 174 megahertz band. The transmitter consists of the following assemblies:

- Transistorized Exciter Board Audio, oscillator, modulator and multiplier stages.
- Transistorized PA Assembly Multiplier, amplifier, power amplifier, low-pass filter and antenna relay.

The transmitter uses 12 transistors to provide an RF power output of 20 Watts. The crystals used range from 6.28 to 7.25 megahertz, and the crystal frequency is multiplied 24 times.

A centralized metering jack (J33) on Systems Board A501 is provided for use with

GE Test Set Models 4EX3A10 or 4EX8K11. The test set meters the phase modulator, multipliers, PA amplifiers, and PA supply voltages. The metering jack also provides access to microphone and push-to-talk leads.

All input leads to the transmitter PA board are individually filtered by feed-through capacitators. Supply voltage, metering and control functions for the exciter board are connected from the Systems Control Unit through a 9-pin miniature connector (PlO5). Supply voltages for the transmitter are shown in the following chart.

Voltage	Use
+12.5 VDC	Amplifiers and PA supply
+12.5 V (Battery)	Relay
Keyed +10VDC	Exciter Board & 2nd doubler

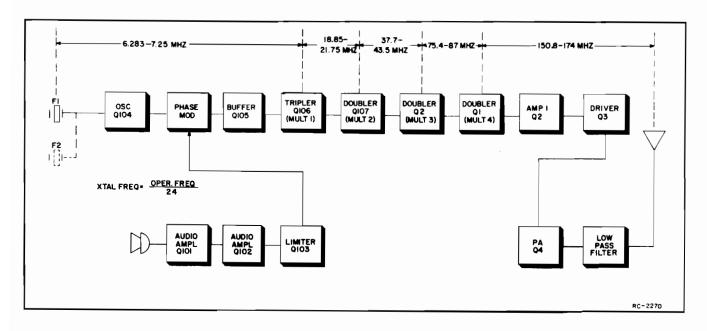


Figure 2 - Transmitter Block Diagram

EXCITER BOARD

OSCILLATOR

A transistorized Colpitts oscillator (Q104) is used in the transmitter. The oscillator crystal is thermistor-compensated at both ends of the temperature range to provide instant frequency compensation with a frequency stability of +.0005% without crystal ovens or warmers. Feedback for the oscillator is developed across C113.

In single-frequency transmitters, a jumper connects the Fl crystal keying lead to ground and the crystal frequency is applied to the base of oscillator A104. The oscillator frequency is adjusted by trimmer C101. The oscillator output is applied to the enode of phase modulator CV101.

In two-frequency transmitters, the single oscillator transistor is used, and an additional crystal circuit and two switching diodes (CR101 and CR102) are added. The keying jumper is removed, and the proper crystal frequency is selected by switching the crystal keying lead to ground by means of a frequency selector switch on the control unit. This forward biases the diode in the crystal circuit, reducing its impedance, so that the selected crystal frequency is applied to the base of oscillator Q104.

AUDIO AMPLIFIER AND LIMITER

The audio section of the transmitter consists of direct-coupled feedback ampli-

fiers Q101, Q102, and Q103. Q103 also acts as a limiter at high audio input levels. Audio from the microphone is coupled through an input network (C132 and R164) to the audio stages. The input network, in conjunction with the feedback circuit, provides the audio gain and a 6-dB/octave pre-emphasis.

The output of limiter Q103 is connected through modulation adjust potentiometer R110 to a de-emphasis network for 6-dB/octave de-emphasis and post limiter roll-off. The network consists of C136, C137, C138, R165 and R166. Modulation Adjust R110 determines the maximum signal level applied to the modulation circuit, and is normally set for $\pm 4.3~\mathrm{kHz}$ (narrow band).

PHASE MODULATOR

The phase modulator uses varactor CV101 (a voltage-variable capacitor) in an R-L-C network that includes R126 and L113. An audio signal applied to the modulator through L113 varies the capacitance of CV101 resulting in a phase modulated output. The modulator output is fed to the base of buffer Q105.

In Channel Guard applications, tone from Channel Guard board Model 4EK14B11 is fed to the modulator circuit through J103 (tone high) and J104 (ground).

BUFFER AND MULTIPLIERS

Buffer stage Q105 isolates the modulator from the loading effects of the tripler stage, and provides some amplification. The output is direct-coupled to the tripler.

Following Q105 are two L-C coupled Class C multiplier stages (Q106 and Q107), Q106 is a tripler stage (MULT-1) with the collector tank tuned to six times the crystal frequency. Resistors R134 and R135 are for metering the doubler stage at centralized metering jack J33.

PA ASSEMBLY

MULTIPLIERS

The exciter output is link-coupled to the base of 2nd doubler Q2 on Systems Board A501. This stage operates as a common emitter doubler and is metered at J33 (MULT-3). The 2nd doubler output is coupled through a series-tuned circuit (tuned to 12 times the crystal frequency) and then through matching network A202 to the base of 3rd doubler Q1 on PA Board A201. This stage is metered at J33 (MULT-4) across A201-R4. The 3rd doubler output is coupled through a series-tuned circuit (tuned to 24 times the crystal frequency) to the base of amplifier Q2.

-WARNING-

The stud-mounted RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

AMPLIFIERS, DRIVER & PA

Q2 operates as a common emitter, series-tuned RF amplifier stage. Base voltage for Q2 is metered at J33 through metering network CR1, R3 and R4.

Driver Q3 follows the amplifier stage. Collector current for Q3 is metered at J33 across resistor R6 on Systems Board A501 (DRIVER Ic). The reading is taken on the 1-Volt scale (the actual current reading is 10 amperes full scale) with the GE Test Set in Position F. The driver output is coupled through a series-tuned circuit to the base of power amplifier Q4.

The power amplifier (Q4) is a commonemitter amplifier providing a minimum RF power output of 20 Watts. Collector current for the PA transistor is measured at J33 (PA Ic) across metering resistor R5 on the Systems Board. The reading is taken on the 1-Volt scale (the current reading is 10 amperes full scale), with the GE Test Set in Position G.

Potentiometer R2 on the Systems Board controls the RF power output of the transmitter by varying the supply voltage to amplifier Q2.

-CAUTION-

Be careful when servicing the PA board as supply voltage is applied continuously to Q1 through Q4.

The power amplifier output is coupled through a series-tuned circuit to low-pass filter FL201, and then through relay K701 to the antenna.

RECEIVER

Receiver Type ER-48-C is a double conversion, superheterodyne FM narrow-band receiver designed for one- or two-frequency operation on the 150.8-174 megahertz band.

The receiver is of single-unit construction and is housed in a copper-plated casting for maximum shielding and rigidity. The unit is completely transistorized, using a total of 20 silicon transistors.

A regulated +10 Volts is used for all receiver stages except the audio driver and audio PA stages, which operate from the 12-Volt system supply. The audio PA stage and output transformer are mounted on the system frame.

Centralized metering jack J304 is provided for use with GE Test Set Model 4EX3AlO. The test set meters the oscillator, lst and 2nd limiters, discriminator, multipliers and audio PA as well as the voice coil, regulated 10 Volts and 12-Volt supply.

RF AMPLIFIERS

RF signals from the antenna are fed to the base of 1st RF amplifier Q301 through two tuned pre-selector circuits. The output signal is inductively coupled through two tuned circuits to the gate of 2nd RF amplifier Q302.

The Second RF Amplifier uses a Field-Effect Transistor (FET) as the active device. The FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied to the control element (gate). Lead identification for the FET is shown in Figure 4.

The FET has several advantages over a conventional transistor, including a high input impedance, high power gain, and an

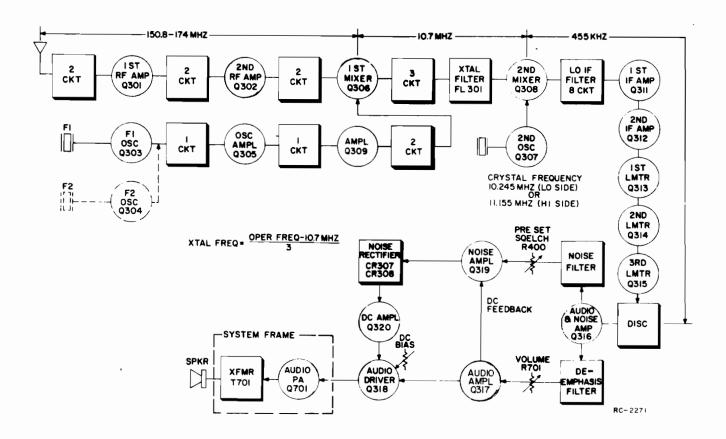


Figure 3 - Receiver Block Diagram

output that is relatively free of harmonics (low in intermodulation products). The FET also has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 4B).

Q302 operates as a grounded-gate amplifier. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the drain terminal and coupled through a tuned circuit (L305, C315 and C316) to the input of the first mixer.

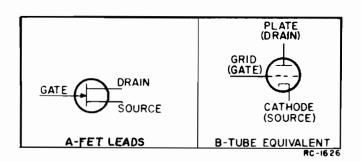


Figure 4 - FET Nomenclature

OSCILLATOR

Q303 is a third mode oscillator that operates in the 40 to 55 megahertz region. The crystal is connected in the oscillator feedback path to permit oscillation only at the crystal frequency. L307, C319 and C320 make up the mode-selective resonant circuit. Adjustable coil L307 permits the oscillator frequency to be shifted slightly for setting the receiver on the system operating frequency. The collector tank of Q303 is tuned to three times the crystal frequency.

For two-frequency operation, a second oscillator stage is added. Channels are selected by grounding the emitter of the desired oscillator by means of a two-frequency switch on the control unit.

1ST MIXER AND CRYSTAL FILTER

The RF signal from the 2nd RF amplifier and the low-side injection voltage from oscillator-amplified Q309 are applied to 1st Mixer Q306.

The 1st Mixer uses a Field-Effect Transistor (FET) as the active device (Figure 4).

RF is applied to the gate of Q306, and injection voltage from the oscillator amplifier is applied to the source. The mixer output is taken from the drain with the output tuned to the 10.7 MHz high IF frequency.

The 10.7 megahertz High IF output is coupled through three tuned circuits (L312 and C350, L313 and C354, L314 and C357) which provide High IF selectivity and impedance matching to the crystal filter.

The Hi-IF crystal filter (FL 301) has ample selectivity to prevent adjacent channel signals from overloading the 2nd Mixer, and to reduce intermodulation spurious responses.

2ND OSCILLATOR AND MIXER

Hi-IF from the crystal filter is applied to the base of 2nd Mixer Q308 with the 10.245-MHz (or 11.155 MHz) 2nd Oscillator output to product the 455-kHz Lo-IF.

The 455-kHz Lo-IF is coupled to an eight-coil Lo-IF filter which provides the main receiver selectivity.

LO-IF AMPLIFIERS AND LIMITERS

Following the Lo-IF filter are two R-C coupled Lo-IF amplifiers (Q311 and Q312). The amplified output is fed to three R-C coupled limiter stages consisting of Q313, Q314 and Q315, operating as overdriver amplifiers. The 1st and 2nd limiter stages are metered at centralized metering jack J304 thru metering diodes CR302 and CR303.

DISCRIMINATOR

The 3rd limiter output is applied to the Foster-Seely type discriminator, where the audio voltages are recovered from the 455-kHz Lo-IF. A low-pass filter, made up of C422, C423, C424, R377, R379 and R380, removes any 455-kHz signal from the discriminator output.

AUDIO AMPLIFIER AND DRIVER

The audio signal is fed to the base of audio-noise amplifier Q316. Following Q316 is an audio de-emphasis network consisting of C426, C427, C428, R383, R384 and R385.

After the de-emphasis network, the audio signal is fed to the base of audio amplifier Q317 through the VOLUME control mounted on the control unit. The VOLUME control is used to set the amount of drive to audio amplifier Q317, audio driver Q318, and audio PA Q701 on the system frame. DC BIAS trimmer R392 sets the bias on Q318 and Q701, and is adjusted for a 250 millivolt (250 milliamps) reading at metering jack J304-9. The output of Q701 drives the loudspeaker.

SQUELCH

Noise from audio-noise amplifier Q316 is used to operate the squelch circuit. When no carrier is present in the receiver, this noise is coupled through a noise filter (which attenuates any audio frequencies) to the base of noise amplifier Q319. The noise filter consists of C435, C436, C437, and L331. The noise level fed to the noise amplifier is set by SQUELCH control R400. The output of noise amplifier Q319 is rectified by diodes CR307 and CR308, and filtered by C441 and C461 to produce a positive DC voltage. This DC voltage turns on DC amplifier Q320, causing it to conduct. When conducting, the collector voltage of the DC amplifier drops to near ground potential which lowers the bias on audio stages Q317 and Q318, turning them off.

As audio amplifier Q317 is being turned off, its emitter potential decreases. This results in a positive DC feedback through R406 to the emitter of noise amplifier Q319 which causes an increase in the gain. As the gain of Q319 increases, the positive DC voltage to the DC amplifier increases, quickly turning the audio stages off.

When the receiver is quieted by a signal, less noise is present in the circuit and the DC amplifier turns off. The audio stages are allowed to conduct, and audio is heard from the speaker. When audio amplifier Q317 is conducting, a positive voltage appears across R406 which helps reduce the gain of noise amplifier Q319. This positive feedback causes a quick, positive switching action in the squelch circuit.

SYSTEM BOARD

System Board A501 contains the 10-Volt regulator, Audio PA stage, Power Level Control stage, the transmitter 2nd doubler circuit (MULT-3), and the transmitter centralized metering jack. The board also provides connection points for all supply voltages for the Two-Way radio. The supply voltages include:

- A continuous, regulated +10 Volts for the receiver and Channel Guard board.
- A keyed, regulated +10 Volts for the transmitter exciter, 2nd doubler (MULT-3), Channel Guard board and receiver muting.
- A continuous +12 Volts for the transmitter, PA board, receiver, and system relay.
- A keyed 12 Volts for the TRANSMIT light.

A simplified power distribution and switching diagram is shown in Figure 5.

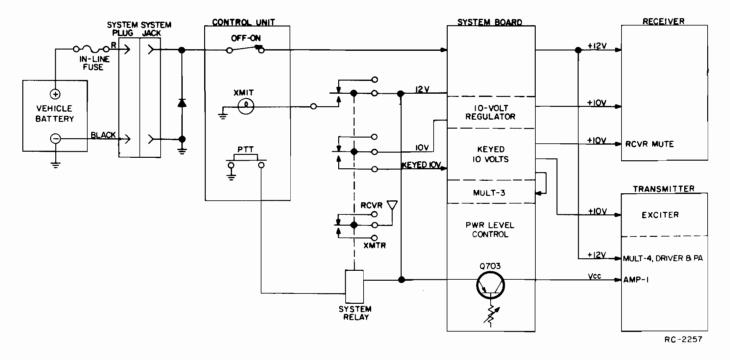


Figure 5 - Power Distribution Diagram

The audio PA, 10-Volt regulator and power level control transistors are mounted on the system frame which acts as a heatsink for these stages.

+10-VOLT REGULATOR

Turning the radio on applies +12 Volts to the collector of regulator transistor Q702, turning it on. The regulated +10 Volts is taken from the emitter of Q702.

When the supply voltage (or output) starts to increase, the voltage at the base of Ql also increases. This causes Ql to conduct more, providing less base current for Q702. The voltage drop across Q702 becomes larger and the output remains constant.

When the input voltage starts to drop, the output voltage also tends to drop and Ql will conduct less. This increases the forward bias on Q702 and reduces the voltage drop across Q702 to keep the output constant.

Potentiometer R10 is used to set the emitter-base voltage of Q1 for the desired 10-Volt output. R7 and R9 limit the maximum current through Q1. R8 provides bias current for Zener diode VR1, and lamp DS1 provides bias for Q702. C2 and C5 prevent high frequency oscillation. The output voltage is metered at receiver centralized metering jack J304.

AUDIO PA

The output of Q318 on the receiver

chassis is applied to the base of the class A, audio PA (Q701). Bias to Q701 is set by DC bias trimmer R392 on the receiver. The trimmer is set for 0.25 Volt at receiver metering jack J304-9 (Position G on GE Test Set). The audio output is coupled through audio transformer T701 and applied to the loudspeaker.

POWER LEVEL CONTROL

Applying power to the radio causes Power Level Control Transistor Q703 to conduct. The output voltage at the collector of Q701 is applied to amplifier Q2 on the PA board. Changing the setting of potentiometer R2 changes the supply voltage to Amplifier Q2, which varies the transmitter power output. Instructions for setting R2 are contained in the transmitter Alignment Procedure.

CONTROL UNIT

The control unit has an OFF-VOLUME control, a MONITOR-SQUELCH switch, a two-frequency switch, a red TRANSMIT light, and a self-contained loudspeaker. Terminal board TB701 is provided for microphone connections.

OFF - VOLUME CONTROL (S701/R701)

The OFF-VOLUME control determines whether the radio is operative or not. Turning S701 On applies supply voltage to the System Board and receiver, and activates the push-to-talk (PTT) circuit.

Pressing the PTT button on the microphone energizes system relay K701. Energizing the relay applies +10 Volts to the exciter board and Channel Guard board, switches the antenna, and mutes the receiver. Energizing the relay also applies +12 Volts to the red TRANSMIT light.

Volume Control R701 is a variable resistor used to control the audio output of speaker LS701.

MONITOR/SQUELCH (S702)

Placing S702 in the MONITOR position disables the noise squelch circuit in the receiver. In radios equipped with Channel Guard, the MONITOR position also disables the receiver Channel Guard.

Placing the switch in the SQUELCH position permits normal operation of the noise squelch and Channel Guard circuits.

TWO-FREQUENCY SWITCHES (S703)

In two-frequency applications, the frequency-selector switch selects the channel

desired for both transmit and receive. The switch connects the emitter of the receiver first oscillator and the transmitter oscillator switching diode to ground, so that the radio will operate on the frequency determined by the selected crystal-controlled oscillators. In two-frequency radios, the transmitter and receiver Channel Guard operate on all frequencies.

CHANNEL GUARD

Channel Guard Board Model 4EK14B11 is a fully transistorized encoder-decoder for use with Custom Executive Mobile combinations.

The tone frequencies are controlled by plug-in tone networks that are made with precision components for excellent stability and reliability. The tone frequencies range from 71.9 to 203.5 Hz.

Complete instructions for the encoder-decoder are contained in Maintenance Manual LBI-4143.

MODULATION LEVEL ADJUSTMENT

The MOD ADJUST (R110) was adjusted to the proper setting before shipment and should not normally require readjustment. This setting permits approximately 75% modulation for the average voice level. The audio peaks which would cause over-modulation are clipped by the modulation limiter, in conjunction with the de-emphasis network, instantaneously limits the slope of the audio wave to the modulator, thereby preventing over-modulation while preserving intelligibility.

TEST EQUIPMENT

- 1. Audio Signal Generator Module 4EX6Al0
- 2. Frequency Modulation Monitor
- 3. AC VTVM or output meter
- 4. GE Test Set Model 4EX3A10 (TM11 or TM12)

PROCEDURE

Transmitters without CHANNEL GUARD

- Connect the audio signal generator and the meter across audio input terminals J5 (Green-Hi) and J6 (Black Lo) on GE Test Set, or across J33-15 (Mike Hi) and J33-7 (Mike Lo) on the Centralized Metering Jack.
- 2. Apply a 0.75 Volt RMS signal at 1000 Hz to Test Set or across J33-15 and J33-7 on the Centralized Metering Jack.
- 3. Set MOD ADJUST (R110) for a 4.3-kHz swing with deviation polarity that gives the highest reading as indicated on the frequency modulation monitor.

Transmitters with CHANNEL GUARD

- 1. Set the Channel Guard TONE ADJUST (R643) for 0.75-kHz tone deviation.
- 2. Follow Steps 1 thru 3 described above.

Two-frequency Transmitters

Check both channels for deviation as described in Steps above.

PA POWER INPUT

For FCC purposes, the PA power input can be determined by measuring the PA supply voltage and PA current, and using the following formula:

P_i + PA voltage x PA current

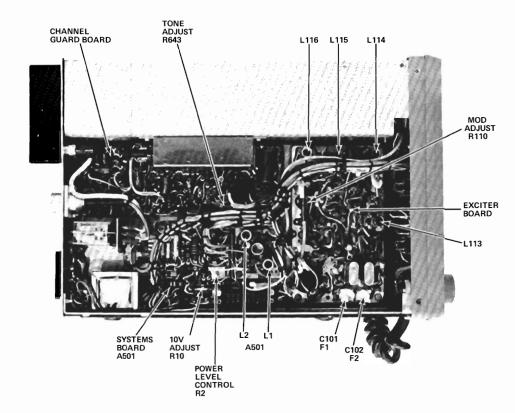
where

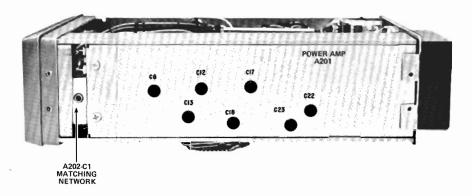
P_i is the power input in Watts,

PA voltage is measured with the GE Test Set in Position G on the 15 Volt scale, and the polarity switch in (-) position,

PA current is measured with the Test Set in Position G in the Test 1 position, and is read as 10 amperes full scale.

Example: $P_i = 12.5 \text{ Volts x 1.5 amperes} = 18.7 \text{ Watts}$





TRANSMITTER ALIGNMENT

LBI-4343

EQUIPMENT REQUIRED

- 1. GE Test Set Model 4EX3A10 (Revision A or later), or Model 4EX8K11.
- 2. A 50-ohm wattmeter connected to Antenna Jack J702
- 3. A frequency counter.

PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Place crystal(s) in crystal socket (crystal frequency = operating frequency + 24).
- 2. For a large change in frequency or a badly misaligned transmitter, set crystal trimmer ClO1 to mid-capacity. In two-frequency transmitters, also set ClO2 to mid-capacity and set the channel selector switch to the highest frequency.
- 3. For a large change in frequency or a badly misaligned transmitter, turn the slugs in the Exciter coils (L113, L114, L115, L116) to the bottom of the coil. Set A501-L1 and -L2 (on System Board) so that the top of the slug is approximately even with the bottom of the coil winding. Adjust C6, C12, C13, C18, C22 and C23 on the PA board 1/2 turn out from the tight position. Adjust C17 1/4 turn out from the tight position.
- 4. Rotate Power Level Control R2 fully clockwise, and adjust A202-Cl 1 turn out from the tight position.

- NOTE

No adjustments should be made on Systems Board A50, Matching Network A202 or PA Board A201 unless Power Control Adjust R2 is in the fully clockwise (maximum power) position.

- 5. Connect the GE Test Set to Receiver Metering jack J302 and check for +10 Volts at Position J. If reading is not 10 Volts, refer to the System Board Outline Diagram and set R10 for +10 Volts.
- 6. Connect GE Test Set to metering jack J33 on Systems Board A501. Set the test polarity to (+) and set the range to the Test 1 (or 1-Volt position for 4EX8K11).
- 7. All adjustments are made with the transmitter keyed. Unkey the transmitter between steps to avoid unnecessary heating.

TRANSMITTER ALIGNMENT PROCEDURE

STEP	METER POSITION	TUNING CONTROL	METER READING	PROCEDURE
				EXCITER BOARD
1.	A (MULT-1)	L113 & L114	See Procedure	Carefully adjust L113 for maximum meter reading. Then adjust L114 for a small dip in meter reading.
2.	B (MULT-2)	L115, L114 & L116	See Procedure	Adjust L115 for maximum meter reading. Re-adjust L114 for maximum meter reading. Then adjust L116 for a dip in meter reading.
				MULT-3, MATCHING NETWORK & PA BOARD
3.	C (MULT-3 INPUT)	A501-L1, L116 & A501-L2	See Procedure	Adjust A501-L1 for maximum meter reading. Next, re-adjust L116 for maximum meter reading. Then adjust A501-L2 for a dip in meter reading.
4.	D (MULT-3 OUTPUT)	A201-C6	Maximum	Adjust A201-C6 for maximum meter reading.
5.	F (DRIVER Ic)	A201-C12, C13 & C6	Maximum	Alternately adjust C12 and C13 several times for maximum meter reading. Then re-adjust C6 for maximum meter reading.
6.	F (DRIVER Ic)	A201-C12 & C13	Maximum	Alternately re-adjust Cl2 and Cl3 for maximum meter reading.
7.	G (PA Ic)	A201-C17 & -C18	Maximum	Alternately adjust C17 and C18 several times for maximum meter reading.
8.	G (PA Ic)	A201-C22 & -C23	Maximum power out; minimum G reading	Alternately adjust C22 and C23 several times for maximum RF power output and minimum PA collector current (Position "G" reading). With meter in Position "G," repeat Steps 8, 7 and 5 in that order for maximum power output.
9.	D (MULT-3 OUTPUT)	A501-L2 & A202-C1	Maximum	Adjust A501-L2 and A202-C1 for maximum meter reading.
10.		A501-R2	20 Watts	Adjust Power Level Control R2 for 20 Watts output maximum.
				FREQUENCY ADJUSTMENT
11.		C101(C102 in 2-freq. units)		Loosely couple frequency counter to output and adjust C101 for proper frequency output. (Switch to F2 and adjust C102 on 2-frequency units.)
				For proper frequency control of the transmitter, it is recommended that all frequency adjustments be made when the equipment is at a temp. of approximately 75° F. In no case should frequency adjustments be made when the equipment is outside the temp. range of 50° to 90° F.

ALIGNMENT PROCEDURE

TRANSMITTER TYPE KT-25-A

Issue 2

11

LBI-4343

TEST PROCEDURES

These Test Procedures are designed to assist you in servicing a transmitter that is operating--but not properly. Problems encountered could be low power output, low supply voltage, tone and voice deviation, defective audio sensitivity and modulator adjust control set too high. By following the sequence of test steps starting with Step 1, the defect can be quickly localized. Once a defect is pin-pointed, refer to the "Service Check" and the additional corrective measures included in the Transmitter Troubleshooting Procedure. Before starting with the Transmitter Test Procedures, be sure the transmitter is tuned and aligned to the proper operating frequency.

TEST EQUIPMENT REQUIRED

for test hookup as shown:

1. Watt meter similar to:

2. VTVM similar to: 3. Audio Generator

Bird #43 Jones #711N Triplett #850 Heath #IM-21

GE MODEL 4EX6A10

4. Deviation Meter (with a .75 kHz scale) similar to:

TEST PROCEDURE

5. Multimeter similar to:

Measurements #140 Lampkin #205A

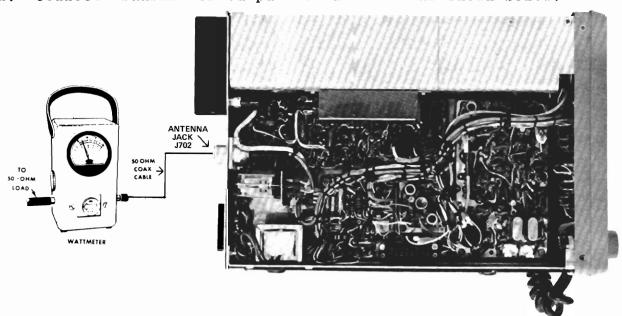
GE TEST SET

MODEL 4EX3A10 or 4EX8K11

STEP 1

POWER MEASUREMENT

A. Connect transmitter output to wattmeter as shown below:



B. Key transmitter and check wattmeter for rated power output.

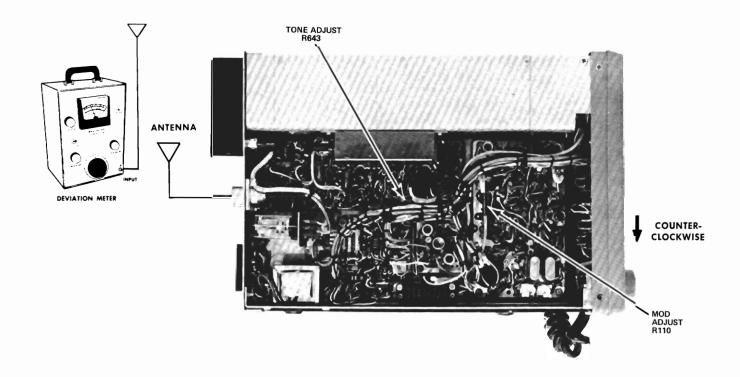
SERVICE CHECK

Refer to Service Hints on Transmitter Troubleshooting Procedure.

STEP 2

TONE DEVIATION WITH CHANNEL GUARD **TEST PROCEDURE**

A. Setup Deviation Meter and monitor output of transmitter as shown below:



- B. Set MOD ADJUST control R110 fully counterclockwise.
- C. Key transmitter and check for 0.75 kHz deviation. If reading is low or high, adjust Channel Guard TONE ADJUST (R643 on Channel Guard Board) for a reading of 0.75 kHz.



DEVIATION METER

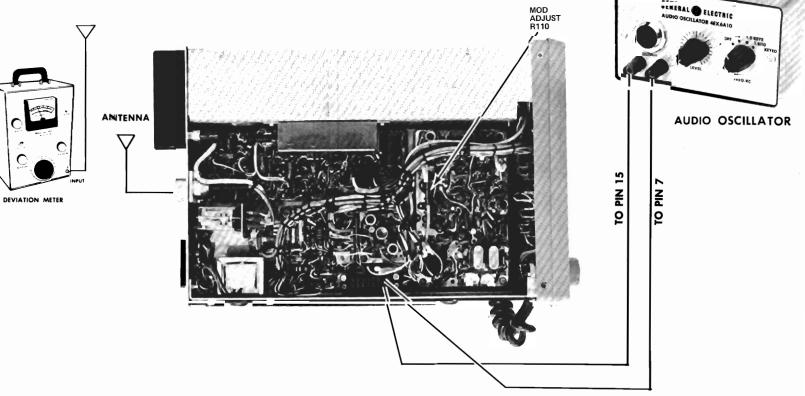
NOTES:

- D. On units supplied with Channel Guard, the Phase Modulator Tuning should be peaked carefully to insure proper performance. (Refer to Step 1 in the Transmitter Alignment Procedure).
- E. The Tone Deviation Test Procedures should be repeated every time the Tone Frequency is changed.

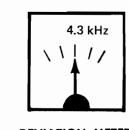
STEP 3

VOICE DEVIATION AND SYMMETRY TEST PROCEDURE

- A. Unplug the microphone.
- B. Connect test equipment to transmitter as shown below:



- C. Set the generator output to 1.0 VOLTS RMS and frequency to 1 kHz.
- D. Key the transmitter by connecting a jumper from TB701-3 to TB701-4 (GRD).
- E. Deviation reading should be ±4.3 kHz.
- F. Adjust MOD ADJUST Control R110 until deviations reads 4.3 kHz on plus (+) or minus (-) deviation, whichever is greater. This adjustment should be made with the correct level of tone applied on Channel Guard transmitters.

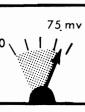


DEVIATION METER

NOTES: -- These transmitters are adjusted for 4.3 kHz deviation at the factory. The factory adjustment will prevent the transmitter from deviating more than 5.0 kHz under the worst conditions of frequency, voltage and temperature.

If the deviation reading plus (+) and minus (-) differs by more than 0.5 kHz, check the following:

- G. Recheck Step 1 as shown in the Transmitter Alignment Procedure.
- H. Check Audio Sensitivity by reducing generator output until deviation falls to 3.3 kHz. Voltage should be LESS than 90 millivolts (typically 75 mv).



METER

FRONT END ALIGNMENT

These instructions are for tuning the oscillator and RF stages of the receiver and may be used when changing the receiver crystal or frequency. When necessary to realign the entire receiver, refer to the COMPLETE RECEIVER ALIGNMENT.

EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3Al0 (TM11 or TM12), 4EX8Kl1 or 20,000 ohms-per-Volt
- 2. 150.8-174 MHz signal source (keep signal level below saturation).

PRELIMINARY CHECKS AND ADJUSTMENTS

STEP METERING POSITION
4EX3A10 Multimeter

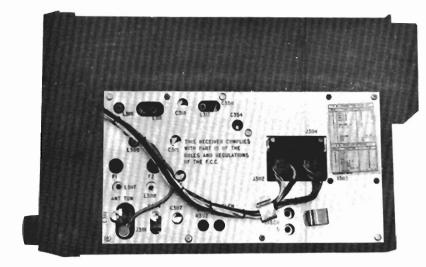
- 1. Plug Test Set 4EX3A10 into receiver centralized metering jack J304. Set meter polarity switch on + and meter sensitivity switch to 1. If using Multimeter, connect the negative lead to J304-13 (ground).
- Turn SQUELCH control (R400) fully clockwise and VOLUME control to minimum. Switch to position "G" (or measure at J304-9 with Multimeter) and set PA Bias R392 for a reading of 0.25 Volt (250 milli-amperes).

TUNING

METER

ALIGNMENT PROCEDURES

STEP	4EX3A10	Multimeter + at J304	TUNING CONTROL	READING	PROCEDURE
1.	D OSC	pin 4	L307	See Procedure	Switch to F1, put in F1 crystal and tune L307 for maximum meter reading.
2.	D OSC	pin 4	L309 & L307	Maximum (.06 - .25)	Apply an on-frequency signal to J301 and adjust L309 and L307 for a maximum meter reading (.0625 Volts).
3.	E OSC	pin 4	L310, L317 & L311	Maximum	Adjust L310, L317 & L311 for maximum.
4.	D OSC	pin 4	L308 (2-freq. only)	Maximum	For 2-frequency receivers, switch to F2, insert F2 crystal and adjust L308 for maximum.
5.					Preset RF capacitors C301, C304, C307, C311, C315, and C318 to approximate-frequency. (Capacitors tune from 130 MC (max. capacitance) to 174 MC (min. capacitance)).
6.	C LIM 2	pin 3	L310, L311 C301, C304 C307, C311 C315, C318	Maximum	Apply on-frequency signal to J301. Tune L310, L311, C301, C304, C307, C311, C315, and C318 for maximum meter reading. Keep signal below saturation at each stage on discriminator zero.
7.	A DISC	pin 10	L307 (L308 for 2-freq.)	Zero	Apply the exact channel frequency signal to J301 and tune L307 (L308 for 2-frequency) for zero discriminator reading.
					For proper freq. control of the receiver, it is recommended that all freq. adjustments be made when the equipment is at a temp. of approx. 75°F. In no case should freq. ad-
					justments be made when the equipment is outside the temp. range of 50° to 90°F.
8.			C301, C304		While receiving a weak on- frequency signal from the antenna, tune C301 and C304 for best quieting.
			SQUELCH ADJUST	MENT	
9.				¥30°	Set SQUELCH Control (R400) to open with a 4 dB SINAD signal. (Approximately 30° counter- clockwise of critical squelch position.)



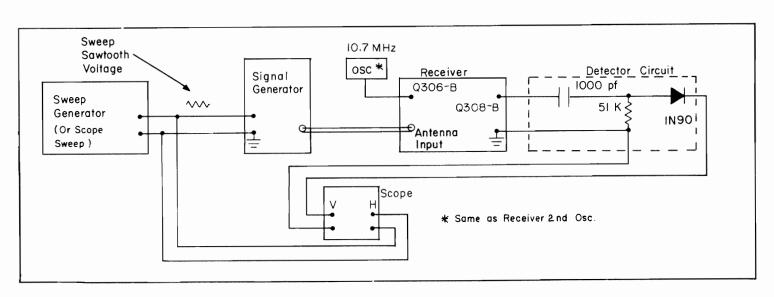


Figure 1 - High and Low IF FILTER TEST Circuit

COMPLETE RECEIVER ALIGNMENT

EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3A10 (TM11 or TM12), 4EX8K11 or 20,000 ohms-per-Volt Multimeter.
- 2. A 10.7 MHz (±200 Hz) and 150.8-174 MHz signal source. Couple the 10.7 MHz signal through a 0.01 µf capacitor. Keep signal levels below
- 3. For Alignment steps 4 thru 8 Oscilloscope, sweep generator, 10.7 MHz marker generator and construct a detector circuit (see Figure 1 for circuitry).

PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Plug Test Set into the receiver centralized metering jack J304. Set meter polarity switch on + and meter sensitivity switch to TEST 1. If using multimeter, connect the negative lead to J304-13 (ground).
- 2. Switch Test Set to Position "I" (or measure at collector of Q318 with multimeter). Reading should be a nominal 13.8 Volts.
- 3. Switch to Position "J" (or measure at top of C443 with multimeter), and check for a reading of 10 Volts. If reading is not correct,
- 4. Turn SQUELCH control fully clockwise and VOLUME control to minimum. Switch to Position "G" (or measure at J304-9 with multimeter) and set PA balas R392 for reading of 0.25 Volts (250 milliamperes).

ALIGNMENT PROCEDURE

STEP	METERANG TEST SIET	POSITION MULTIMETER + at J304	TUNING CONTROL	METER READING	PROCEDURE
					DISCRIMINATOR
1.					Remove 1st oscillator crystal and apply a 10.7 MHz signal to the base of Q308.
2.	A DISC	pin 10	L329	See Procedure	Adjust L329 (discriminator primary) 1/2 turn up from bottom of range.
3.	A DISC	pin 10	L330	Zero	Tune L330 (discriminator secondary) for zero meter reading.
	24			Н	IGH and LOW IF FILTER (SEE NOTE 1)
4.	B LIM	pin 2	L321 thru L328	Maximum	Adjust L321 thru L328 for maximum meter reading.
5.	B	pin 2	C357, C354, C350	See Procedure	Adjust C357 for minimum meter reading. Adjust C354 for maximum meter reading. Adjust C350 for minimum meter reading.
6.			C357 & C360		Disable the 2nd oscillator by grounding base of Q307 through a .01 μf capacitor. Connect scope, signal generator and detector as shown in figure 1. Sweep RF ± 50 kHz at 20 Hz. Connect 10.7 MHz marker to gate of Q306. Tune C357 and C360 for scope pattern shown. Keep marker signal centered between humps and signal level below saturation.
7.			L321 thru L328		Disconnect detector, remove short from base of Q307 and connect scope to 1st LIM test point. Adjust L321 thru L328 for symetrical wave form shown, with marker in center.
8.	A DISC	pin			Check to see that discriminator idling voltage is within 0.05 Volts of zero with no signals applied and the modulation acceptance band width is greater than $\pm 8~\mathrm{kHz}$ (narrow band).
					OSC/MULT & AMPLIFIER
9.	D OSC	pin 4	L307	Maximum	Remove short from base of Q307, if present, then insert 1st oscillator crystal and adjust L307 for maximum meter reading.
10.	D OSC	pin 4	L309 & L307	Maximum (.0625 V)	Adjust L309 and L307 for maximum meter reading (.0625 Volts).
11.	E OSC	pin 4	L310, L317 L311	Maximum	Adjust L310, L317 and L311 for maximum.
12.	D OSC	pin 4	L308 (2-freq)	Maximum	For 2-frequency receiver, insert F2 crystal and adjust L308 for maximum meter reading.
					RF
13.	C LIM 2	pin 3	L321, L322, L323, L324, L325, L326, L327, L328	Maximum	Inject 10.7 MHz crystal-controlled marker on base of 2nd Mixer Q308. Adjust L321, L322, L323, L324, L325, L326, L327, L328, for maximum meter reading. Keep signal below saturation at each stage and on discriminator zero. Remove 10.7 MHz marker.
14.	C LIM 2	pin 3	C350, C354, C357, C360	Maximum	Inject 10.7 MHz crystal-controlled marker to gate of Q306. Adjust C350, C354, C357 and C360 for maximum meter reading. Adjust C350 for dip on "B" position of test meter.
15.			C301, C304		While receiving a weak on-frequency signal from the antenna, tune C301 and C304 for best quieting.
16.	A DISC	pin 10	L307 (L308 for 2 freq.)	Zero	Apply the exact channel frequency signal to J301 and tune L307 (L308 for 2-frequency) for zero discriminator reading. NOTE————————————————————————————————————
					For proper frequency control of the receiver, it is recommended that all frequency adjustments be made when the equipment is at a temp. of approx. $75^{\circ}F$. In no case should frequency adjustments be made when the equipment is outside the temp. range of 50° to $90^{\circ}F$.
17.				√30°	Set SQUELCH Control (R400) to open with a 4 dB SINAD signal. (Approximately 30° counterclockwise of critical squelch position.)

ALIGNMENT PROCEDURE

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RECEIVER MODELS 4ER48C10-15 FOR MOBILE COMBINATIONS

NOTE 1 -- High and Low IF coils and capacitors have been set at the factory and will normally require no further adjustment. Do not re-

Issue 1

TEST PROCEDURES

These Test Procedures are designed to help you to service a receiver that is operating——but not properly. The problems encountered could be low power, poor sensitivity, distortion, limiter not operating properly, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized. Once

TEST EQUIPMENT REQUIRED

- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-800
- 6-dB attenuation pad, and 3.2 ohm, 10-Watt resistor

the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

PRELIMINARY ADJUSTMENTS

- 1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure.
- 2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
- 3. Turn on all of the equipment and let it warm up for 20 minutes.

SIGNAL GENERATOR CHANNEL FREQUENCY OUTPUT DEVIATION CONTROL OUTPUT OUTPUT

INPUT LEVEL CONTROL RANGE CONTROL (SET LEVEL & DISTORTION RANGE) 2 4 6 9 11 13

REMOVE JUMPER BETWEEN P701-2 AND P702-3 AND CONNECT A 312-OHM, 10 WATT RESISTOR BETWEEN P701-2 AND

STEP 1

AUDIO POWER OUTPUT AND DISTORTION TEST PROCEDURE

Measure Audio Power Output as follows:

- A. Connect a 1,000-microvolt test signal modulated by 1,000 hertz with +3.3 kHz deviation to the antenna jack J301.
- B. When speaker is used, disconnect speaker (and handset if present). Hook up a 3.2-ohm load resistor on P701 as shown. C.
- C. Set VOLUME Control for one-Watt output (1.77 VRMS).
- D. Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%.

SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than one Watt, make the following checks:

- E. Battery and regulator voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- F. Set SQUELCH control R400 fully counterclockwise and volume control to minimum. Switch to position G on test set and check to see if Bias is set at 0.25 Volt (250 mA).
- G. Audio Gain (Refer to Receiver Troubleshooting Procedure).
- H. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

STEP 2 USABLE SENSITIVITY (12-dB SINAD)

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

- A. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.3-kHz deviation to J301.
- B. Place the RANGE switch on the Distortion Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.).
- C. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).
- D. While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).
- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specifications with an audio output of at least one Watt (1.77 Wolts RMS across the 3.2-ohm receiver load using the Distortion Analyzer as a VTVM).
- F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be performed.

SERVICE CHECK

If the sensitivity level is more than rated 12 dB SINAD specification, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

STEP 3 MODULATION ACCEPTANCE BANDWITH (IF BANDWITH)

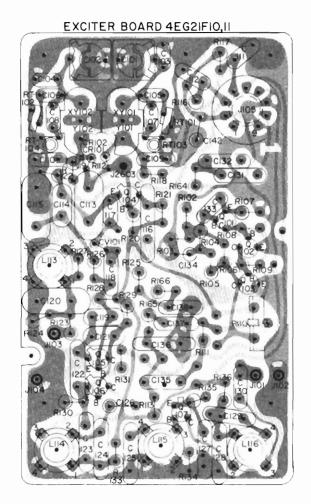
If STEPS 1 and 2 check out properly, measure the bandwidth as follows:

- A. Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.
- B. Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.
- C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).
- D. The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than ±8 kHz (but less than ±10 kHz).

SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

OUTLINE DIAGRAM



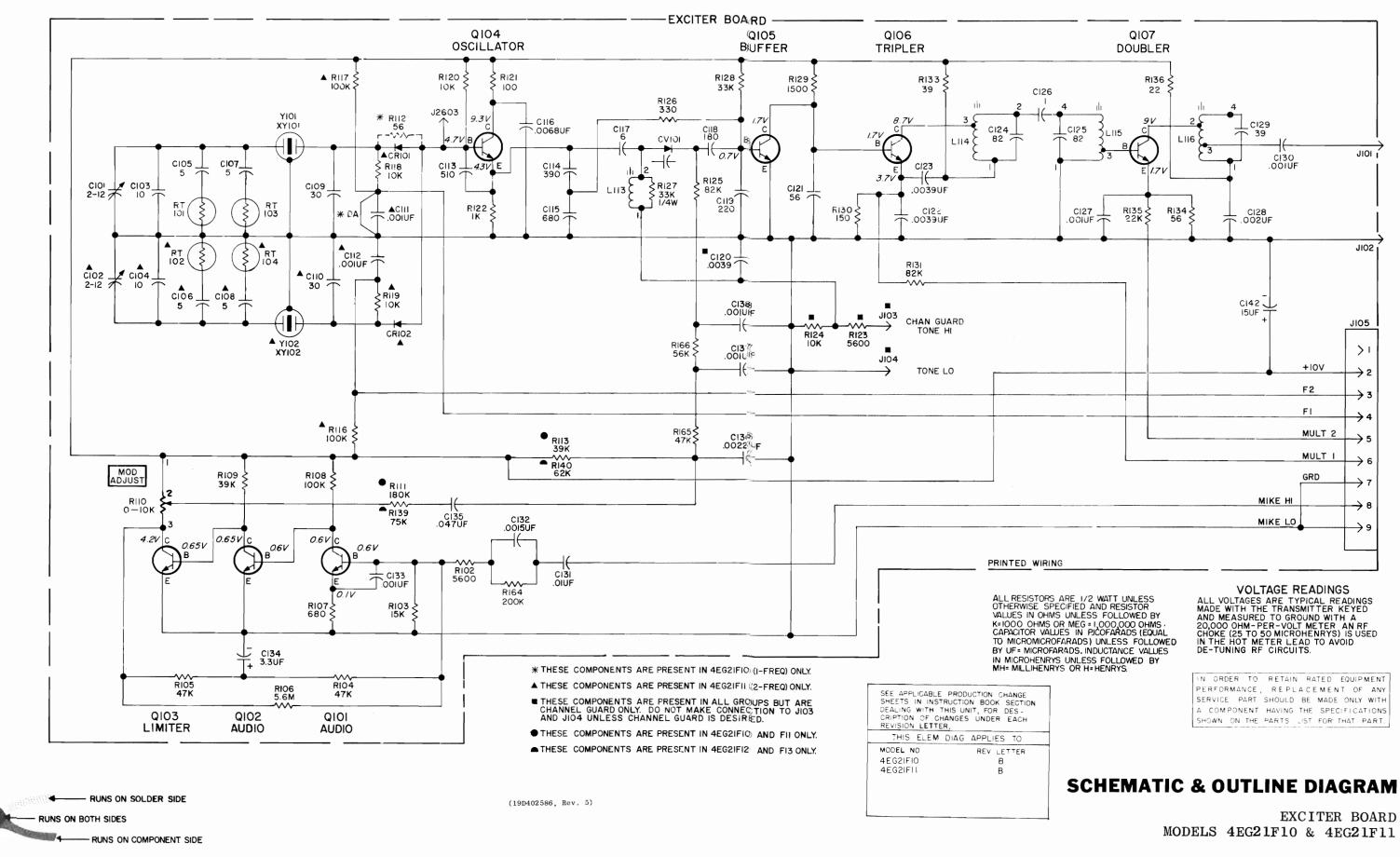
(19E500954, Rev. 5) (19B205178, Sh. 1, Rev. 1) (19B205178, Sh. 2, Rev. 1)

RESISTANCE READINGS

ALL READINGS ARE TYPICAL READINGS MEASURED FROM TRANSISTOR PINS TO GROUND WITH ALL POWER TURNED OFF, READINGS ON THE EXCITER BOARD OVER 1,000 OMMS READ ON THE X 1,000 SCALE. + OR — SIGN SHOW METER | FAD GROUNDED.

EXCITER BOARD

TRANSISTOR	EMITTER		BAS	E	COLLECTOR	
SYMBOL #		+		+	-	+
Q101	650	650	13.200	3.650	8600	2800
Q102			8.600	2.800	12,000	2800
Q103			12 000	3.800	10.000	11,500
Q104	1000	1000	14.000	3.500	2500	3000
Q105			35.000	3.300	4300	3300
Q106_	150	150	4.300		2900	2900
Q107	50	50			2600	2900



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PARTS LIST

LBI-4349 EXCITER BOARD MODEL 4EG21F10 1 FREQ NARROW BAND MODEL 4EG21F11 2 FREQ NARROW BAND

-80 PPM. C122 and C123 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C124 5496219P261 Ceramic disc: 82 pf ±5%, 500 VDCW, temp -80 PPM. C125 T130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp coe approx 0 PPM; sim to Jeffers Type JM-5/32 C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .39 pf ±5%, 500 VDCW, temp -80 PPM. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: .001 pf ±20%, 500 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL.	
C102 C103 and C104 C105 C105 C105 C105 C106 C107 C108 C109 C109 C109 C109 C109 C109 C109 C109	
coef 0 PPM. Commit of the coef of PPM. Ceramic disc: 5 pf ±0.1 pf, 500 VDCW, temp of PPM.	v peak;
COOP O PPM. COOP	temp
O PPM. C111	emp
RMC Type JF Discap. C113 5496372P167 Ceramic disc: 510 pf ±10%, 500 VDCW, ter-300 PPM. C114 5493366P390J Silver mica: 390 pf ±5%, 100 VDCW; sim to Electro Motive Type DM-15. C115 5493367P680J Silver mica: 680 pf ±5%, 100 VDCW; sim to Electro Motive Type DM-20. C116 5494481P131 Ceramic disc: .0068 pf ±20%, 1000 VDCW; RMC Type JF Discap. C117 5496219P37 Ceramic disc: 6 pf ±0.25 pf, 500 VDCW, temp-2000 PPM. C118 5496372P46 Ceramic disc: 180 pf ±5%, 500 VDCW, temp-2000 PPM. C119 5490008P135 Silver mica: 220 pf ±10%, 500 VDCW; sim Electro Motive Type DM-15. C120 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C121 5496219P218 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C122 and C123 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C124 5496219P261 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C125 C126 7130348P3 Moldel: 1 pf ±.05 pf, 500 VDCW, temp-80 PPM. C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C130 5494481P11 Ceramic disc: .001 pf ±10%, 500 VDCW, temp-80 PPM. C131 19B209243P1 Polyester: 0.01 µf ±20%, 50 VDCW, s RMC Type JF Discap. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JF Discap.	coef
C114 5493366P390J Silver mica: 390 pf ±5%, 100 VDCW; sim to Electro Motive Type DM-15. C115 5493367P680J Silver mica: 680 pf ±5%, 100 VDCW; sim to Electro Motive Type DM-20. C116 5494481P131 Ceramic disc: .0068 pf ±20%, 1000 VDCW; RMC Type JF Discap. C117 5496219P37 Ceramic disc: 6 pf ±0.25 pf, 500 VDCW, temp -2200 PPM. C118 5496372P46 Ceramic disc: 180 pf ±5%, 500 VDCW, temp -2200 PPM. C119 5490008P135 Silver mica: 220 pf ±10%, 500 VDCW; sim Electro Motive Type DM-15. C120 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C121 5496219P218 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C122 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C123 C124 5496219P261 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C126 7130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp -80 PPM. C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C120 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C130 5494481P112 Ceramic disc: .001 pf ±10%, 500 VDCW, temp -80 PPM. C131 19B209243P1 Polyester: .001 pf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .001 pf ±20%, 50 VDCW.	sim to
Electro Motive Type DM-15. 5493367P680J Silver mica: 680 pf ±5%, 100 VDCW; sim telectro Motive Type DM-20. C116 5494481P131 Ceramic disc: .0068 pf ±20%, 1000 VDCW; RMC Type JF Discap. C117 5496219P37 Ceramic disc: 180 pf ±5%, 500 VDCW, temp -2200 PPM. C118 5496372P46 Ceramic disc: 180 pf ±5%, 500 VDCW, temp -2200 PPM. C119 5490008P135 Silver mica: 220 pf ±10%, 500 VDCW; sim Electro Motive Type DM-15. C120 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C121 5496219P218 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C122 and C123 C124 5496219P261 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C125 C126 7130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp -80 PPM. C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P112 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 pf ±20%, 50 VDCW. Ceramic disc: .001 pf ±10%, 500 VDCW; s RMC Type JF Discap. C132 7491395P111 Ceramic disc: .001 pf ±20%, 50 VDCW.	mp coef
Electro Motive Type DM-20. C116 5494481P131 Ceramic disc: .0068 pf ±20%, 1000 VDCW; RMC Type JF Discap. C117 5496219P37 Ceramic disc: 6 pf ±0.25 pf, 500 VDCW, temp-2200 PPM. C118 5496372P46 Ceramic disc: 180 pf ±5%, 500 VDCW, temp-2200 PPM. C119 5490008P135 Silver mica: 220 pf ±10%, 500 VDCW; sim Electro Motive Type DM-15. C120 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C121 5496219P218 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C122 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C123 C124 5496219P261 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C126 7130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp-80 PPM. C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; semp-80 PPM. C130 5494481P112 Ceramic disc: .002 pf ±20%, 1000 VDCW; semp-80 PPM. C131 19B209243P1 Polyscap. C132 7491395P111 Ceramic disc: .001 pf ±10%, 500 VDCW; semp-91 properser	to
RMC Type JF Discap. C117 5496219P37 Ceramic disc: 6 pf ±0.25 pf, 500 VDCW, temp -2200 PPM. C118 5496372P46 Ceramic disc: 180 pf ±5%, 500 VDCW, temp -2200 PPM. C119 5490008P135 Silver mica: 220 pf ±10%, 500 VDCW; sim Electro Motive Type DM-15. C120 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C121 5496219P218 Ceramic disc: 56 pf ±10%, 500 VDCW, temp -80 PPM. C122 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C123 C124 5496219P261 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C125 C126 7130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp -80 PPM. C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 µf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s RMC Type JL.	to
C018 5496372P46 Ceramic disc: 180 pf ±5%, 500 VDCW, temp-2200 PPM. C119 5490008P135 Silver mica: 220 pf ±10%, 500 VDCW; sim Electro Motive Type DM-15. C120 5494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C121 5496219P218 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C122 and C123 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C124 5496219P261 Ceramic disc: 82 pf ±5%, 500 VDCW, temp-80 PPM. C125 C126 7130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp-80 PPM. C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; RMC Type JF Discap. C128 5494481P112 Ceramic disc: .002 pf ±20%, 1000 VDCW; small composition of the second composition o	sim to
C119	temp
Electro Motive Type DM-15.	coef
RMC Type JF Discap. C121 5496219P218 Ceramic disc: 56 pf ±10%, 500 VDCW, temp-80 PPM. C122 and C123 Ceramic disc: .0039 pf ±20%, 1000 VDCW; RMC Type JF Discap. C124 5496219P261 Ceramic disc: 82 pf ±5%, 500 VDCW, temp-80 PPM. C125 7130348P3 Molded: 1 pf ±.05 pf, 500 VDCW, temp-80 PPM; sim to Jeffers Type JM-5/32 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P112 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .002 pf ±5%, 500 VDCW, temp-80 PPM. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 pf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s RMC Type JL.	to
-80 PPM. Ceramic disc: .0039 pf ±20%, 1000 VDCW; and C123 S494481P129 Ceramic disc: .0039 pf ±20%, 1000 VDCW; and C123 Ceramic disc: 82 pf ±5%, 500 VDCW, temp -80 PPM. Ceramic disc: 82 pf ±5%, 500 VDCW, temp -80 PPM. Ceramic disc: .001 pf ±0%, 1000 VDCW; sm to Jeffers Type JM-5/32 Ceramic disc: .001 pf ±10%, 1000 VDCW; sm to Jeffers Type JM-5/32 Ceramic disc: .002 pf ±20%, 1000 VDCW; sm to Jeffers Type JF Discap. Ceramic disc: .002 pf ±20%, 1000 VDCW; sm to Jeffers Type JF Discap. Ceramic disc: .001 pf ±10%, 1000 VDCW; sm to Jeffers Type JF Discap. Ceramic disc: .001 pf ±10%, 1000 VDCW; sm to Jeffers Type JF Discap. Ceramic disc: .001 pf ±10%, 1000 VDCW; sm to Jeffers Type JF Discap. Ceramic disc: .001 pf ±20%, 50 VDCW. Ceramic disc: .0015 pf ±10%, 500 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Ceramic disc: .001 pf ±20%, 1000 VDCW; sm to Jeffers Type JL. Cerami	sim to
RMC Type JF Discap. C124 and C125 C126 7130348P3 Molded: l pf ±.05 pf, 500 VDCW, temp coe approx 0 PPM; sim to Jeffers Type JM-5/32 C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .39 pf ±5%, 500 VDCW, temp -80 PPM. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 pf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. Ceramic disc: .001 pf ±20%, 500 VDCW; s RMC Type JL.	coef
SO PPM. Sim to Jeffers Type JM-5/32 Molded: l pf ±.05 pf, 500 VDCW, temp coe approx 0 PPM; sim to Jeffers Type JM-5/32 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. Ceramic disc: .002 pf ±5%, 500 VDCW, temp -80 PPM. Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. Ceramic disc: .001 pf ±10%, 500 VDCW; s RMC Type JF Discap. Ceramic disc: .001 pf ±10%, 500 VDCW; s RMC Type JF Discap. Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. Ceramic disc: .001 pf ±20%, 500 VDCW; s RMC Type JL. Ceramic disc: .001 pf ±20%, 1000 VD	sim to
approx 0 PPM; sim to Jeffers Type JM-5/32 C127 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .39 pf ±5%, 500 VDCW, temp -80 PPM. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 µf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	coef
RMC Type JF Discap. C128 5494481P113 Ceramic disc: .002 pf ±20%, 1000 VDCW; s RMC Type JF Discap. C129 5496219P253 Ceramic disc: .39 pf ±5%, 500 VDCW, temp -80 PPM. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 μf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	ef 2.
RMC Type JF Discap. C129 5496219P253 Ceramic disc: 39 pf ±5%, 500 VDCW, temp -80 PPM. C130 5494481P112 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. C131 19B209243P1 Polyester: 0.01 µf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	sim to
-80 PPM. Cl30 5494481Pl12 Ceramic disc: .001 pf ±10%, 1000 VDCW; s RMC Type JF Discap. Cl31 19B209243Pl Polyester: 0.01 µf ±20%, 50 VDCW. Cl32 7491395Pl11 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. Cl33 5494481Pl11 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	sim to
RMC Type JF Discap. 19B209243P1 Polyester: 0.01 µf ±20%, 50 VDCW. C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	coef
C132 7491395P111 Ceramic disc: .0015 pf ±10%, 500 VDCW; s RMC Type JL. C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	im to
RMC Type JL. C133 5494481Pll1 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	
C133 5494481P111 Ceramic disc: .001 pf ±20%, 1000 VDCW; s	im to
1	im to
C134 5496267P9 Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	
Cl35 19All6080P5 Polyester: 0.047 μf ±20%, 50 VDCW.	
Cl36 7491395Pl14 Ceramic disc: .0022 pf ±10%, 500 VDCW; s RMC Type JL.	im to
C137 7491395P109 Ceramic disc: .001 pf ±10%, 500 VDCW; si RMC Type JL.	m to

Pacific Semiconductor Varicap Type V-596.	SYMBOL	GE PART NO.	DESCRIPTION
CRIOL 19A1156391	C142	5496 2 67 P 14	
CX102 CY101 S495769P9 Varactor, silicon: 33 µf ±10% at 4 VDC; sim to Pacific Semiconductor Varicap Type V-596. JACKS AND RECEPTACLES JOHN AND RECEPTACLES JOHN AND RECEPTACLES Contact, electrical: sim to Bead Chain 193-3. J104 J105 J108 J108 J109 J109 J109 J109 J109 J109 J109 J109			DIODES AND RECTIFIERS
Varactor, silicon: 33 μf ±10% at 4 VDC; sim to Pacific Semiconductor Varicap Type V-596.		19A115603P1	Silicon,
Jin		5495769 P 9	
J101 thru J105			JACKS AND RECEPTACIES
Cart of Exciter Board 19G303835p1). Coll. Includes tuning slug 5491798P2.	thru	4033513P4	
Lill 19C303883G13	J105	19B209303P1	Connector, phen: 9 pins.
Lili Lili Lili Lili Lili Lili Lili Lili	J 2603		(Part of Exciter Board 19C303835P1).
Lili 19C303883G13 Coil. Includes tuning slug 5491798P2. Lili 19C303883G14 Coil. Includes tuning slug 5491798P2. Lili 19C303883G15 Coil. Includes tuning slug 5491798P2. Lili 19C303883G17 Coil. Includes tuning slug 5491798P2. Lili 29C303883G17 Coil. Includes tuning slug 5491798P2. Lili 29C30383G17 Coil. Includes tuning slug 5491798P2. Lili 29C30383G17 Composition: 5600 ohms ±10%, 1/2 w. Lili 29C3038716 Composition: 5600 ohms ±10%, 1/2 w. Lili 29C3038716 Composition: 680 ohms ±10%, 1/2 w. Lili 29C3038716 Composition: 100 ohms ±10%, 1/2 w. Lili 29C303371 Composition: 82,000 ohms ±10%, 1/2 w. Lili 29C303371 Composition: 330 ohms ±5%, 1/4 w. Lili 29C3038716 Composition: 330 ohms ±5%, 1/4 w. Lili 29C3038716 Composition: 330 ohms ±5%, 1/4 w. Lili 29C303371 Composition: 330 ohms ±5%, 1/4 w. Lili 29C303371 Composition: 330 ohms ±5%, 1/4 w. Lili 38C3038716 Composition: 330 ohms ±5%, 1/4 w. Lili 38C3038716 Composition: 330 ohms ±5%, 1/4 w. Lili 38C3038716 Compositi			INDUCTORS
Lil4 19C303883G14 Coll. Includes tuning slug 5491788P2. Lil5 19C303883G15 Coll. Includes tuning slug 5491788P2. Lil6 19C303883G17 Coll. Includes tuning slug 5491788P2. Lil6 19C303883G17 Coll. Includes tuning slug 5491788P2. Lil6 19A115889P1 Silicon, NFN. Lil6 19A115123P1 Silicon, NFN; sim to Type 2N2712. Lil6 19C300114P1 Silicon, NFN; sim to Type 2N2712. Lil6 19C300114P1 Silicon, NFN; sim to Type 2N706. Lil6 19A115330P1 Silicon, NFN. Lil6 19A115328P1 Silicon, NFN. Lil6 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. Lil6 3R77P473J Composition: 15,000 ohms ±5%, 1/2 w. Lil6 3R77P473J Composition: 47,000 ohms ±5%, 1/2 w. Lil6 3R77P565J Composition: 5.6 megohms ±5%, 1/2 w. Lil6 3R77P681K Composition: 680 ohms ±10%, 1/2 w. Lil6 3R77P393K Composition: 0.1 megohm ±10%, 1/2 w. Lil6 3R77P393K Composition: 0.1 megohm ±10%, 1/2 w. Lil6 19E209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w. Lil1 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. Lil1 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. Lil1 3R77P104K Composition: 0.18 megohm ±10%, 1/2 w. Lil1 3R77P104K Composition: 0.10 megohm ±10%, 1/2 w. Lil1 3R77P104K Composition: 0.10 megohm ±10%, 1/2 w. Lil1 3R77P104K Composition: 100 ohms ±10%, 1/2 w. Lil1 3R77P103K Composition: 100 ohms ±10%, 1/2 w. Lil1 3R77P103K Composition: 100 ohms ±10%, 1/2 w. Lil1 3R77P103K Composition: 100 ohms ±10%, 1/2 w. Lil1 3R152P33J Composition: 330 ohms ±5%, 1/4 w. Lil1 3R152P33J Composition: 330 ohms ±5%, 1/4 w. Lil1 3R152P33J Composition: 330 ohms ±5%, 1/4 w. Lil1 3R152P33J Compositi	L113	19C303883G13	
1115		İ	
Coil. Includes tuning slug 5491798P2.	L115	19C303883G15	
Q101 19A115889P1 Silicon, NPN. Silicon, NPN; sim to Type 2N2712. Q104 19C300114P1 Silicon, NPN; sim to Type 2N706. Q105 19A115330P1 Silicon, NPN. Q106 19A115328P1 Silicon, NPN. Q107	L116	19C303883G17	
Q101			
Q102 and Q103 19A115123P1 Silicon, NPN; sim to Type 2N2712. Q104 19C300114P1 Silicon, NPN; sim to Type 2N706. Q105 19A115330P1 Silicon, NPN. Q106 and Q107 Silicon, NPN. Q108 19A115328P1 Silicon, NPN. Q109 Silicon, NPN. Q109 Silicon, NPN. Q100 Silicon, NPN. Q100 Silicon, NPN. Q101 Silicon, NPN. Q101 Silicon, NPN. Q102 Silicon, NPN. Q103 Silicon, NPN. Q104 Silicon, NPN. Q105 Silicon, NPN. Q106 Silicon, NPN. Q107 Silicon, NPN. Q108 Silicon, NPN. Q109 Silicon, NPN. Q109 Silicon, NPN. Q100 Silicon, NPN. 0101	104115000		
and quo3 quo4 19C300114P1 Silicon, NPN; sim to Type 2N706. Q105 19Al15330P1 Silicon, NPN. Q106 and quo7			1
Q104 19C300114P1 Silicon, NPN; sim to Type 2N706. Q105 19Al15330P1 Silicon, NPN. Q106 and Q107	and	19A115123Pl	Silicon, NPN; sim to Type 2N2712.
Q105		19030011401	Silicon NDN, cim to True ONGO
Q106 and q107 Silicon, NPN. Silicon, NPN.			
And Q107 R102 R102 R103 R77P562K Composition: 5600 ohms ±10%, 1/2 w. Composition: 15,000 ohms ±5%, 1/2 w. R104 R105 R106 R106 R106 R107 R107 R107 R107 R107 R107 R108 R108 R108 R109 R109 R109 R100 R			
R102 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R103 3R77P153J Composition: 15,000 ohms ±5%, 1/2 w. R104 3R77P473J Composition: 47,000 ohms ±5%, 1/2 w. R105 3R77P565J Composition: 5.6 megohms ±5%, 1/2 w. R106 3R77P681K Composition: 680 ohms ±10%, 1/2 w. R107 3R77P681K Composition: 0.1 megohm ±10%, 1/2 w. R108 3R77P104K Composition: 39,000 ohms ±10%, 1/2 w. R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R118 3R77P103K Composition: 100 ohms ±10%, 1/2 w. R120 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P103K Composition: 5600 ohms ±10%, 1/2 w. R122 3R77P103K Composition: 5600 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/4 w.	and		Sizzon, Min.
R102 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R103 3R77P153J Composition: 15,000 ohms ±5%, 1/2 w. R104 and R105 R106 3R77P473J Composition: 47,000 ohms ±5%, 1/2 w. R106 3R77P565J Composition: 5.6 megohms ±5%, 1/2 w. R107 3R77P681K Composition: 680 ohms ±10%, 1/2 w. R108 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 R118 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R119 3R77P104K Composition: 10,000 ohms ±10%, 1/2 w. R120 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R122 3R77P103K Composition: 5600 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P331J Composition: 82,000 ohms ±10%, 1/2 w. R127 3R152P333J Composition: 330 ohms ±5%, 1/4 w.			RESISTORS
R103 3R77P153J Composition: 15,000 ohms ±5%, 1/2 w. R104 and R105 R106 3R77P473J Composition: 47,000 ohms ±5%, 1/2 w. R106 3R77P681K Composition: 5.6 megohms ±5%, 1/2 w. R107 3R77P681K Composition: 680 ohms ±10%, 1/2 w. R108 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 R118 3R77P104K Composition: 10,000 ohms ±10%, 1/2 w. R120 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 5600 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/4 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R102	3R77P562K	
R104 and R105 R106 R106 R106 R106 R106 R106 R106 R106	R103	3R77P153J	
and RR105 R106 3R77P565J Composition: 5.6 megohms ±5%, 1/2 w. R107 3R77P681K Composition: 680 ohms ±10%, 1/2 w. R108 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 R118 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R120 R121 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R123 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 5600 ohms ±10%, 1/2 w. R125 3R77P331J Composition: 82,000 ohms ±10%, 1/2 w. R125 3R77P331J Composition: 330 ohms ±5%, 1/4 w. Composition: 330 ohms ±5%, 1/4 w. Composition: 33,000 ohms ±5%, 1/4 w.	R104	3R77P473J	
R107 3R77P681K Composition: 680 ohms ±10%, 1/2 w. R108 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 R118 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R120 3R77P103K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.			
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R108 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 0.1 megohm ±10%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 3R77P104K Composition: 10,000 ohms ±10%, 1/2 w. R118 thru R120 3R77P103K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R107	3R77P681K	
R109 3R77P393K Composition: 39,000 ohms ±10%, 1/2 w. R110 19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201. R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 0.1 megohm ±10%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R120 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 100 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P331J Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. Composition: 33,000 ohms ±5%, 1/4 w.	R108	3R77P104K	
19B209358P106 Variable, carbon film: 75 to 10,000 ohms ±10%, 1/4 w; sim to CTS Type X-201.	R109	3R77P393K	
R111 3R77P184J Composition: 0.18 megohm ±5%, 1/2 w. R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R118 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R120 3R77P101K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R110	19B209358P106	Variable, carbon film: 75 to 10,000 ohms ±10%,
R112 3R152P560J Composition: 56 ohms ±5%, 1/4 w. R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. R116 3R77P104K Composition: 0.1 megohm ±10%, 1/2 w. R117 R118 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R120 3R77P101K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 5600 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R111	3R77P184J	
R113 3R77P393J Composition: 39,000 ohms ±5%, 1/2 w. Composition: 0.1 megohm ±10%, 1/2 w. R116 3R77P104K Composition: 10,000 ohms ±10%, 1/2 w. R118 thru R120 3R77P103K Composition: 100 ohms ±10%, 1/2 w. R121 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.			
Ril6 and Ril7 Composition: 0.1 megohm ±10%, 1/2 w. Ril8 and Ril7 Composition: 10,000 ohms ±10%, 1/2 w. Ril8 arryplo3K Composition: 100 ohms ±10%, 1/2 w. Ril20 3R77Pl03K Composition: 100 ohms ±10%, 1/2 w. Ril22 3R77Pl02K Composition: 1000 ohms ±10%, 1/2 w. Ril23 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. Ril24 3R77Pl03K Composition: 10,000 ohms ±10%, 1/2 w. Ril25 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. Ril26 3R77P331J Composition: 330 ohms ±5%, 1/2 w. Ril27 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.			
and and R117 R118 R119 R119 R119 R119 R119 R119 R119			
thru R120 R121 3R77P101K Composition: 100 ohms ±10%, 1/2 w. R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.			
R122 3R77P102K Composition: 1000 ohms ±10%, 1/2 w. R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	thru	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R121	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.
R123 3R77P562K Composition: 5600 ohms ±10%, 1/2 w. R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R122	3R77P102K	, , , , , , ,
R124 3R77P103K Composition: 10,000 ohms ±10%, 1/2 w. R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R123	3R77P562K	
R125 3R77P823K Composition: 82,000 ohms ±10%, 1/2 w. R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R124	3R77P103K	· · · · · · · · · · · · · · · · · · ·
R126 3R77P331J Composition: 330 ohms ±5%, 1/2 w. R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	R125	3R77P823K	
R127 3R152P333J Composition: 33,000 ohms ±5%, 1/4 w.	126	3R77P331J	
	R127		
	R128		, , , , , , , , , , , , , , , , , , , ,
R129 3R77P152K Composition: 1500 ohms ±10%, 1/2 w.	R129	3R77P152K	, , , , , , , , , , , , , , , , , , , ,
R130 3R77P151K Composition: 150 ohms ±10%, 1/2 w.	R130	3R77P151K	,

	SYMBOL	GE PART NO.	DESCRIPTION
1	R131	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
	R133	3R77P390K	Composition: 39 ohms ±10%, 1/2 w.
	R134	3R77P560K	Composition: 56 ohms ±10%, 1/2 w.
	R135	3R77P223K	Composition: 22,000 ohms ±10%, 1/2 w.
1	R136	3R77P220K	Composition: 22 ohms ±10%, 1/2 w.
	R164	3R77P204J	Composition: 0.20 megohm ±5%, 1/2 w.
1	R165	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.
	R166	3R77P563J	Composition: 56,000 ohms ±5%, 1/2 w.
		5M77F0030	Composition: 36,000 onas 15%, 1/2 w.
	RT101	19B209353P2	THERMISTORS Disc: 460 ohms max; sim to GE 16D-3121.
	and RT102 RT103	19B209353P1	Rod: 10,200 ohms min; sim to GE 1R-1544.
	and RT104	100200011	NOC. 10,200 0Hms min, Sim to the in-1344.
			SOCKETS
	XY101 and		Includes:
	XY102	4033089Pl	Clip. (Part of XY101, 102).
		19Al15793Pl	Contact, electrical: sim to Malco 2700.
			(Part of XY101, 102).
		19C311172P1	Socket, crystal. (Part of XY101, 102).
		19B200525P9	Rivet. (Part of XY101, 102).
			When reordering give GE Part Number and specify
			exact frequency needed.
			Crystal freq = (OF : 24).
	Y101 and	19B206204P1	Quartz: freq range 5400-7250 KHz, temp range -30°C to +85°C.
	Y102		-50 € 20 465 €.
П			

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped on the unit includes all previous revisions. Refer to the Parts List for description of parts affected by these revisions.

REV. A & B - Incorporated into initial shipment.

PA BOARD

2 C21 | Lie C21

RESISTANCE READINGS

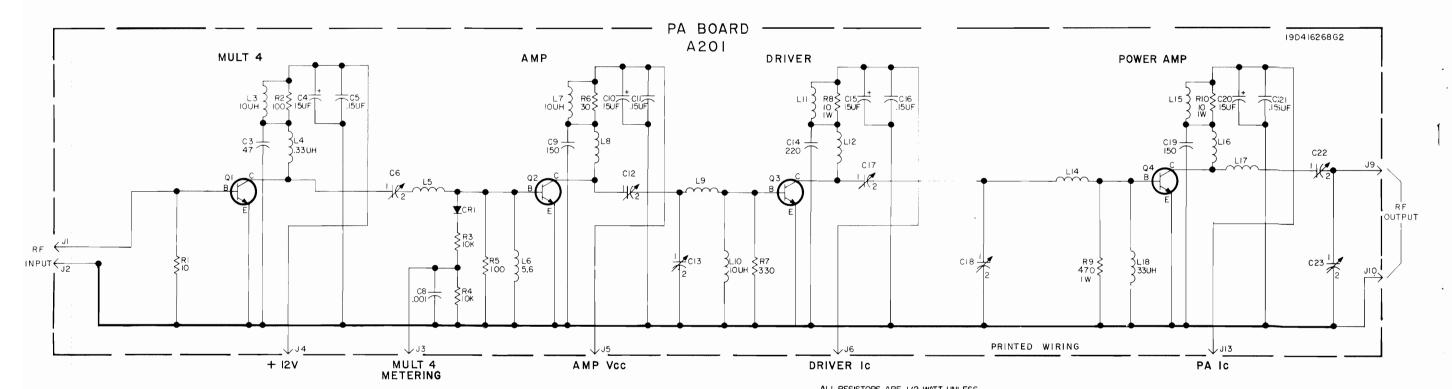
ALL READINGS ARE TYPICAL READINGS MEASURED FROM TRANSISTOR PINS TO GROUND WITH ALL POWER TURNED OFF, READINGS ON THE EXCITER BOARD OVER 1,000 OHMS READ ON THE X 1,000 SCALE. + OR — SIGN SHOW METER LEAD GROUNDED.

(19E500954, Rev. 5) (19D416266, Sh. 1, Rev. 2) (19D416266, Sh. 2, Rev. 2)

	PA	ASSEME	BLY			
SYMBOL ,	ЕМ	ITTER	E	BASE	COLI	ECTOR
#	-	+		+	-	+
QI (2ND DOUBLER A201)	9.5	10.2	9.6	10.5	40	200
QI(3RD DQUBLER A202)	GND	GND	1,1		3.1h	
Q2 IST AMP	GND	GND	.4	0.4	5. !K	5.4K
Q3 DRIVER	GND	GND	(2	0.2	- 5.6K	-11.3K
Q4 PA	GND	GHO	8.6	8.4	3 K	5.4 K
	GND	GND				
			-		Marine Committee	

SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEAL NO WITH THIS UNIT, FOR DES. CRIPTION OF CHANGES UNDER EACH REVISION. LETTER THIS ELEM DIAG APPLIES TO MODEL NIC REV LETTER 19D4162688G2 A

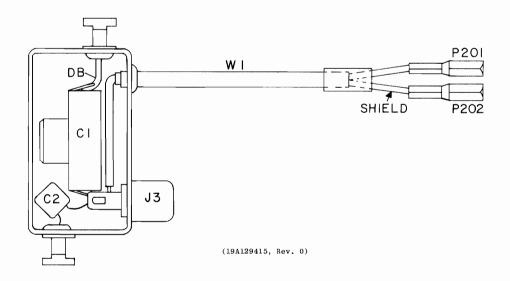
SCHEMATIC DIAGRAM



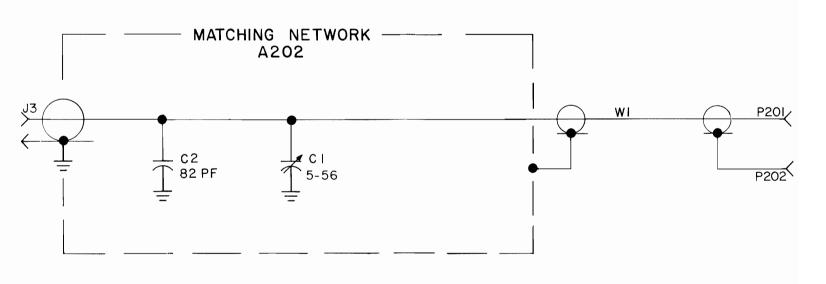
IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS OF A CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS, INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

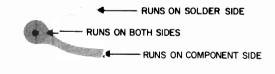
OUTLINE DIAGRAM



SCHEMATIC DIAGRAM



(19B219575, Rev. 3)



SCHEMATIC & OUTLINE DIAGRAMS

PA BOARD 19D416268G2 AND MATCHING NETWORK 19C320162G1

Issue 3

17

LBI-4343

PARTS LIST

LBI-4350A

PA BOARD 19D416268G2 WITH MATCHING NETWORK 19C320162G1

RMC Type JF Discap.	YMBOL	GE PART NO.	DESCRIPTION
C3	A201		
Electro Motive Type DN-15.			
Sprague Type 150D. Sprague Type 150D. Sprague Type 150D. Polyester: 0.15 µf ±20%, 50 VDCW. Variable, mica: 4-25 pf, 400 VDCW. Service State of the Committed Sprague Type 150D. Sprague Type JF Discap. Committed Sprague Type 150D. Committed	С3	7489162P119	
C6	C4	5496267P14	
C8 19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. C10 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C11 19A116080P8 Polyester: 0.15 µf ±20%, 50 VDCW. C12 19B209408P2 Variable, mica: 4-25 pf, 400 VDCW. C13 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C14 19A116055P10 Ceramic disc: 220 pf ±10%, 1000 VDCW; sim to Sprague Type 150D. C15 5496267P14 Tantalum: 15 µf ±20%, 20 VDCW; sim to Sprague Type 150D. C16 19A116080P8 Polyester: 0.15 µf ±20%, 50 VDCW. C17 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C18 19A116055P14 Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C20 5496267P14 Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C21 19A116080P8 Polyester: 0.15 µf ±20%, 50 VDCW. C22 19B209408P3 Variable, mica: 37-140 pf, 400 VDCW. C23 19B209408P3 Variable, mica: 37-140 pf, 400 VDCW. C24 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C25 19B209408P3 Variable, mica: 37-140 pf, 400 VDCW. C26 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C27 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C28 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C29 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C20 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C21 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C31 19A115250P1 Terminal; sim to Alcon 3-1215. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim to Bead Chain L93-3. C31 19A116080P8 Contact, electrical: sim t	C5	19A116080P8	Polyester: 0.15 µf ±20%, 50 VDCW.
RNC Type JF Discap. Cleamic disc: 150 pf ±10%, 1000 VDCW; sim to RNC Type JF Discap. Clo 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. Cl1 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. Cl2 19B209408P2 Variable, mica: 4-25 pf, 400 VDCW. Cl3 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. Cl4 19A116655P10 Ceramic disc: 220 pf ±10%, 1000 VDCW; sim to RNC Type JF Discap. Cl5 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. Cl6 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. Cl7 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. Cl9 19A116655P14 Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RNC Type JF Discap. C20 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. C21 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. C22 19B209408P6 Variable, mica: 37-140 pf, 400 VDCW. C23 19B209408P6 Variable, mica: 7-50 pf, 400 VDCW. C24 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C25 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C26 19B15250P1 Silicon. CR1 19A115250P1 Silicon. CR1 19A115250P1 Terminal; sim to Alcon 3-1215. COntact, electrical: sim to Bead Chain L93-3. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J15 Terminal; sim to Alcon 3-1215. Contact, electrical: sim to Bead Chain L93-3. Choke, RF: 10.0 μh ±10%, 0.60 ohms DC res max sim to Jeffers 4421-7K. L4 7488079P3 Choke, RF: 0.33 μh ±20%, 0.07 ohms DC res max sim to Jeffers 4421-7M. Choke, RF: 0.30 μh ±10%, 0.60 ohms DC res max sim to Jeffers 4421-7M. Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4421-7M. Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M. Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M. Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M.	C6	19B209408P2	Variable, mica: 4-25 pf, 400 VDCW.
RMC Type JF Discap. Tantalum: 15 \(\psi \) f 220\(\psi \), 20 VDCW; sim to Sprague Type 150D. C11 19A116080P8 Polyester: 0.15 \(\psi \) f 220\(\psi \), 50 VDCW. C12 19B209408P2 Variable, mica: 4-25 \(pf \), 400 VDCW. C13 19B209408P3 Variable, mica: 7-50 \(pf \), 400 VDCW. C14 19A116655P10 Ceramic disc: 220 \(pf \) f 10\(\psi \), 1000 VDCW; sim to RMC Type JF Discap. C15 5496267P14 Tantalum: 15 \(pf \) f 220\(\psi \), 20 VDCW; sim to Sprague Type 150D. C16 19A116080P8 Polyester: 0.15 \(pf \) f 220\(\psi \), 30 VDCW. C17 19B209408P3 Variable, mica: 7-50 \(pf \), 400 VDCW. C19 19A116655P14 Ceramic disc: 470 \(pf \) f 10\(\psi \), 1000 VDCW; sim to RMC Type JF Discap. C20 5496267P14 Tantalum: 15 \(\psi \) f 220\(\psi \), 20 VDCW; sim to Sprague Type 150D. C21 19A116080P8 Polyester: 0.15 \(\psi \) f 220\(\psi \), 30 VDCW. C22 19B209408P6 Variable, mica: 37-140 \(pf \), 400 VDCW. C23 19B209408P3 Variable, mica: 7-50 \(pf \), 400 VDCW. C24 19B209408P3 Variable, mica: 7-50 \(pf \), 400 VDCW. C25 19B209408P3 Variable, mica: 7-50 \(pf \), 400 VDCW. C26 19A115250P1 Silicon. C7 19A115250P1 Silicon. C8 19A115250P1 Silicon. C9 19A115250P1 Terminal; sim to Alcon 3-1215. C9 19A115250P1 Terminal; sim to Alcon 3-1215. C17 19A115250P1 Terminal; sim to Alcon 3-1215. C18 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C19 19A115250P1 Contact, electrical: sim	C8	19A116655P19	Ceramic disc: 1000 pf $\pm 20\%$, 1000 VDCW; sim to RMC Type JF Discap.
Sprague Type 150D.	C9	19A116655P8	Ceramic disc: 150 pf \pm 10%, 1000 VDCW; sim to RMC Type JF Discap.
C12	C10	5496267P14	
C13	C11	19A116080P8	Polyester: 0.15 μf ±20%, 50 VDCW.
C14 19A116655P10 Ceramic disc: 220 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C15 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. C16 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. C17 and 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C19 19A116655P14 Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C20 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. C21 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. C22 19B209408P6 Variable, mica: 37-140 pf, 400 VDCW. C23 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. CR1 19A115250P1 Silicon. CR1 19A115250P1 Silicon. CR1 4033513P4 Contact, electrical: sim to Bead Chain L93-3. dand J10 J13 4033284P2 Terminal; sim to Alcon 3-1215. C99 4033513P4 Contact, electrical: sim to Bead Chain L93-3. dand J10 J13 4033284P2 Terminal; sim to Alcon 3-1215. C19 Contact, electrical: sim to Bead Chain L93-3. dand J10 J13 4033284P2 Terminal; sim to Alcon 3-1215. C19 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J15 Contact, electrical: sim to Bead Chain L93-3. dand J16 Contact, electrical: sim to Bead Chain L93-3. dand J16 Contact, electrical: sim to Bead	C12	19B209408P2	Variable, mica: 4-25 pf, 400 VDCW.
RMC Type JF Discap. C15 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. C16 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. C17 and 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C19 19A116655P14 Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C20 5496267P14 Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. C21 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. C22 19B209408P6 Variable, mica: 37-140 pf, 400 VDCW. C23 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. CR1 19A115250P1 Silicon. CR1 19A115250P1 Silicon. CR1 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J16 4033284P2 Terminal; sim to Alcon 3-1215. J29 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J10 J13 4033284P2 Terminal; sim to Alcon 3-1215. C19 Contact, electrical: sim to Bead Chain L93-3. C19 Contact, electrical: sim to Bead Chain L93-3. C10 Contact, electrical: sim to Bead Chain L93-3. C11 Contact, electrical: sim to Bead Chain L93-3. C12 Contact, electrical: sim to Bead Chain L93-3. C13 Contact, electrical: sim to Bead Chain L93-3. C14 Contact, electrical: sim to Bead Chain L93-3. C15 L9B216275P5 Coil. C16 7488079P13 Choke, RF: 0.33 μh ±20%, 0.07 ohms DC res max sim to Jeffers 4411-3M. C16 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M. C17 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M. C18 C19 CP	C13	19B209408P3	Variable, mica: 7-50 pf, 400 VDCW.
Sprague Type 150D.	C14	19A116655P10	Ceramic disc: 220 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
C17 and C18 C18 C18 C19 19A116655P14 Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C15	5496267P14	
C19	C16	19A116080P8	Polyester: 0.15 μf ±20%, 50 VDCW.
RMC Type JF Discap.	and	19B209408P3	Variable, mica: 7-50 pf, 400 VDCW.
Tantalum: 15 μf ±20%, 20 VDCW; sim to Sprague Type 150D. C21 19A116080P8 Polyester: 0.15 μf ±20%, 50 VDCW. C22 19B209408P6 Variable, mica: 37-140 pf, 400 VDCW. C23 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. C24 19A115250P1 Silicon. C25 19A115250P1 Silicon. C26 19A115250P1 Silicon. C37 19A115250P1 Contact, electrical: sim to Bead Chain L93-3. C38 19A115250P1 Terminal; sim to Alcon 3-1215. C39 19A13284P2 Terminal; sim to Alcon 3-1215. C39 19A13284P2 Terminal; sim to Alcon 3-1215. C39 19A13313P4 Contact, electrical: sim to Bead Chain L93-3. C39 19A134 19A13284P2 Terminal; sim to Alcon 3-1215. C4033284P2 Terminal; sim to Alcon 3-1215. C50114 19A13284P2 Terminal; sim to Alcon 3-1215. C60000 Terminal; sim to Alcon 3-1215. C7488079P16 Choke, RF: 10.0 μh ±10%, 0.60 ohms DC res max sim to Jeffers 4421-7K. C60000 Terminal; Sim to Jeffers 4421-7K. C7488079P3 Choke, RF: 0.33 μh ±20%, 0.07 ohms DC res max sim to Jeffers 4411-3M. C7488079P13 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M. C6000 Terminal; Sim to Alcon 3-1215. C6000 Terminal; Sim to Alcon 3-1215. C7488079P13 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M. C6000 Terminal; Sim to Alcon 3-1215. C6000 Terminal; Sim to Alcon 3-1215. C7488079P13 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M.		19A116655P14	Ceramic disc: 470 pf $\pm 10\%$, 1000 VDCW; sim to RMC Type JF Discap.
C22 19B209408P6 Variable, mica: 37-140 pf, 400 VDCW. C23 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. CR1 19A115250P1 Silicon. CR1 19A115250P1 Silicon. CONTACT, electrical: sim to Bead Chain L93-3. J6 4033284P2 Terminal; sim to Alcon 3-1215. J9 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J13 4033284P2 Terminal; sim to Alcon 3-1215. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J15 Contact, electrical: sim to Bead Chain L93-3.	C20	5496267P14	Tantalum: 15 µf ±20%, 20 VDCW; sim to
C23 19B209408P3 Variable, mica: 7-50 pf, 400 VDCW. DIODES & RECTIFIERS Silicon. JACKS & RECEPTACLES J1 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J6 4033284P2 Terminal; sim to Alcon 3-1215. J9 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J13 4033284P2 Terminal; sim to Alcon 3-1215. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J15 Contact, electrical: sim to Bead Chain L93-3.	C21	19A116080P8	Polyester: 0.15 µf ±20%, 50 VDCW.
CR1 19A115250P1 Silicon. JACKS & RECEPTACLES J1 thru J5 J6 4033284P2 Terminal; sim to Alcon 3-1215. J9 and J10 J13 4033284P2 Terminal; sim to Alcon 3-1215. Contact, electrical: sim to Bead Chain L93-3. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J15 J16 4033284P2 Terminal; sim to Alcon 3-1215. Contact, electrical: sim to Bead Chain L93-3. J17 4033513P4 Contact, electrical: sim to Bead Chain L93-3.	C22	19B209408P6	Variable, mica: 37-140 pf, 400 VDCW.
CRI 19A115250P1 Silicon. JACKS & RECEPTACLES J1 thru J5 J6 4033284P2 Contact, electrical: sim to Bead Chain L93-3. J9 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J10 4033284P2 Terminal; sim to Alcon 3-1215. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J15 Contact, electrical: sim to Bead Chain L93-3.	C23	19B209408P3	Variable, mica: 7-50 pf, 400 VDCW.
J1 thru J5			DIODES & RECTIFIERS
11 thru	CRl	19A115250P1	Silicon.
11 thru			JACKS & RECEPTACLES
J6 4033284P2 Terminal; sim to Alcon 3-1215. J9 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J13 4033284P2 Terminal; sim to Alcon 3-1215. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. L3 7488079P16 Choke, RF: 10.0 µh ±10%, 0.60 ohms DC res massim to Jeffers 4421-7K. L4 7488079P3 Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res massim to Jeffers 4411-3M. L5 19B216275P5 Coil. L6 7488079P13 Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res massim to Jeffers 4411-3M.	thru	4033513P4	
J9 and J10 J13 4033284P2 Terminal; sim to Alcon 3-1215. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. J15 Contact, electrical: sim to Bead Chain L93-3. L3 7488079P16 Choke, RF: 10.0 µh ±10%, 0.60 ohms DC res maxim to Jeffers 4421-7K. L4 7488079P3 Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res maxim to Jeffers 4411-3M. L5 19B216275P5 Coil. Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res maxim to Jeffers 4411-3M.		4033284P2	Terminal; sim to Alcon 3-1215.
J13 4033284P2 Terminal; sim to Alcon 3-1215. J14 4033513P4 Contact, electrical: sim to Bead Chain L93-3. L3 7488079P16 Choke, RF: 10.0 µh ±10%, 0.60 ohms DC res massim to Jeffers 4421-7K. L4 7488079P3 Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res massim to Jeffers 4411-3M. L5 19B216275P5 Coil. L6 7488079P13 Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res massim to Jeffers 4411-3M.	J9 and	4033513P4	,
J14 and J15 Contact, electrical: sim to Bead Chain L93-3.		402255475	monday to the second
and J15 INDUCTORS Choke, RF: 10.0 μh ±10%, 0.60 ohms DC res max sim to Jeffers 4421-7K. L4 7488079P3 Choke, RF: 0.33 μh ±20%, 0.07 ohms DC res max sim to Jeffers 4411-3M. L5 19B216275P5 Coil. L6 7488079P13 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res max sim to Jeffers 4411-3M.			
L3 7488079P16 Choke, RF: 10.0 μh ±10%, 0.60 ohms DC res ma: sim to Jeffers 4421-7K. L4 7488079P3 Choke, RF: 0.33 μh ±20%, 0.07 ohms DC res ma: sim to Jeffers 4411-3M. L5 19B216275P5 Coil. L6 7488079P13 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res ma:	and	4033513P4	Contact, electrical: sim to Bead Chain L93-3
sim to Jeffers 4421-7K. Choke, RF: 0.33 µh ±20%, 0.07 ohms DC res massim to Jeffers 4411-3M. L5 19B216275P5 Coil. L6 7488079P13 Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res massim to Jeffers 4411-3M.			INDUCTORS
sim to Jeffers 4411-3M. L5 19B216275P5 Coil. L6 7488079P13 Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res ma:	L3	7488079P16	
L6 7488079Pl3 Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res max	L4	7488079P3	
L6 7488079P13 Choke, RF: 5.60 μh ±10%, 0.30 ohms DC res ma: sim to Jeffers 4421-4K.	L5	19B216275P5	Coil.
	L6	7488079P13	Choke, RF: 5.60 µh ±10%, 0.30 ohms DC res massim to Jeffers 4421-4K.

SYMBOL	GE PART NO.	DESCRIPTION
L7	7488079P16	Choke, RF: 10.0 μh $\pm 10\%$, 0.60 ohms DC res max; sim to Jeffers 4421-7K.
L8	19A129167P1	Coil.
L9	19B219376P1	Coil.
L10	7488079P16	Choke, RF: 10.0 µh ±10%, 0.60 ohms DC res max; sim to Jeffers 4421-7K.
L11	7488079P40	Choke, RF: 5.60 µh ±10%, 0.15 ohms DC res max; sim to Jeffers 4422-1K.
L12	19B219376P2	Coil.
L14	19A129281P1	Coil,
L15	19B216365G1	Coil.
L16	19B219376P1	Coil.
L17	19A129166P1	Coil.
L18	7488079P49	Choke, RF: 33.0 μh ±10%, 1.90 ohms DC res max;
		sim to Jeffers 4422-10K.
L19	19A129282P1	Coil.
Q1 and Q2	19A129181P1	Silicon, NPN.
Q3	19A129181P3	Silicon, NPN.
Q4	19A129181P4	Silicon, NPN.
		, in the second
		RESISTORS
R1	3R77P100K	Composition: 10 ohms ±10%, 1/2 w.
R2	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.
R3 and R4	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
R5	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.
R6	3R77P300J	Composition: 30 ohms ±5%, 1/2 w.
R7*	3R77P331J	Composition: 330 ohms ±5%, 1/2 w.
		Earlier than REV A:
	3R77P910K	Composition: 91 ohms ±10%, 1/2 w.
R8	3R78P100K	Composition: 10 ohms ±10%, 1 w.
R9*	3R78P471K	Composition: 470 ohms ±10%, 1 w.
		Earlier than REV A:
	3R78P101K	Composition: 100 ohms ±10%, 1 w.
R10	3R78P100K	Composition: 10 ohms ±10%, 1 w.
		· ·
A202		MATCHING NETWORK 19C320162G1
C1	19B209408P3	Variable, mica: 7 to 50 pf, 400 VDCW.
C2	19All6288Pll	Ceramic: 82 pf ±5%, 100 VDCW; sim to Erie 8121-100-COG-820J.
		JACKS & RECEPTACLES
J3	7104941P20	Receptacle, coaxial: sim to National Tel.
P201	4029840P2	Contact, electrical: sim to Amp 42827-2.
P202	4029840P1	Contact, electrical: sim to AMP 41854.
W1	19B209044P13	RF: approx 3 inches long; sim to Amphenol
		421-105.
		MISCELLANEOUS
	19C317960P1	Heat sink.
	7147306P2	Washer, shoulder: No. 6, black pressed fiber; sim to H.H. Smith Inc 2150. (Used with L15).
	5492178P2	Washer, spring tension: sim to Wallace Barnes 375-20. (Used with Q1-Q4).

18 *COMPONENTS ADDED DI

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - PA Board (19D416268G2)

To improve power output. Changed R7 and R9

^{*}COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

PARTS LIST

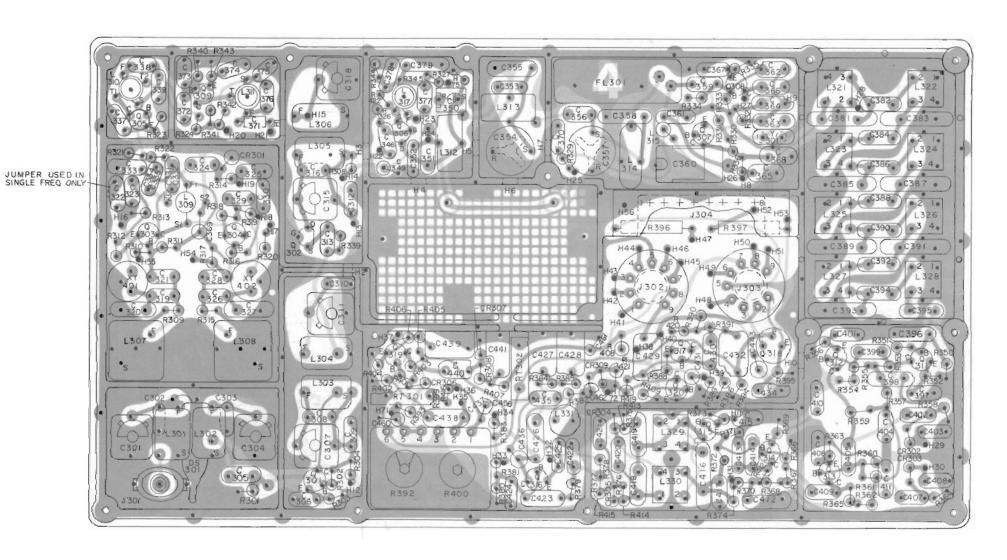
LBI-4257C

132-174 MHz RECEIVER MODELS 4ER48C10-15

SYMBOL	GE PART NO.	DESCRIPTION
		CAPACITORS
C301	5491271P106	Variable, air: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C302	19A116656P5J8	Ceramic disc: 5 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C303	19A116656P5J2	Ceramic disc: 5 pf ±0.5 pf, 500 VDCW, temp coef -220 PPM.
C304	5491271P106	Variable, air: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C305	5490008P131	Silver mica: 150 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C306	19Al16655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C307	5491271P106	Variable, air: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C308	19A116656P5J2	Ceramic disc: 5 pf ±0.5 pf, 500 VDCW, temp coef -220 PPM.
C309	7491827P102	Ceramic disc: .01 µf +80%-30%, 50 VDCW; sim to Sprague 19C180.
C310	19A116656P5J3	Ceramic disc: 5 pf ±0.5 pf, 500 VDCW, temp coef -330 PPM.
C311	5491271P106	Variable, air: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C312	7491827P102	Ceramic disc: .01 µf +80% -30%, 50 VDCW; sim to Sprague 19C180.
C313	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C315	5491271Pl06	Variable, air: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C316	19A116656P5J2	Ceramic disc: 5 pf ±0.5 pf, 500 VDCW, temp
C318	5491271P106	Variable, air: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C319A	5496219P447	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef
C319B	5496219P444	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -220 PPM.
C320A	5496219P357	Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef
C320B	5496219P356	-80 PPM. Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef
C321A and C321B	5496219 P 34	-150 PPM. Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C322	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C323	19A116656P3J0	Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
C324	5496219 P 34	Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C325	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C326A	5496219P447	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef -220 PPM.
С326В	5496219P444	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef
C327A	5496219P357	-220 PPM. Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef
С327В	5496219P356	-150 PPM. Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef
	5496219 P 34	-150 PPM. Ceramic disc: 3 pf ±0,25 pf, 500 VDCW, temp

SYMBOL	GE PART NO.	DESCRIPTION
C329	5496219 P 34	Ceramic disc: 3 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C330	19A116655P19	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C331A	5496219P744	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef
C331B*	5496219P740	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef -750 PPM.
		In REV A and earlier:
	5496219P741	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -750 PPM.
C332A	5496219P744	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -750 PPM.
C332B*	5496219P740	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef -750 PPM.
		In REV A and earlier:
	5496219P741	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -750 PPM.
C333	19A116655P19	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C334	5496219P36	Ceramic disc: 5 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C335	5496219P38	Ceramic disc: 7 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C337	19A116655P19	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C338A	5496219P241	Ceramic disc: 10 pf ±5%, 500 VDCW, temp coef -80 PPM.
C338B	5496219P238	Ceramic disc: 7 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C339	19A116655P19	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C346	19A116655P19	Ceramic disc: .001 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C349	5496267P10	Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
C350	19A116462P3	Variable: less than 2 pf to more than 20 pf, 100 VDCW, -320 PPM/*C.
C351*	19C300685P248	Ceramic disc: 62 pf ±2%, 500 VDCW, temp coef -80 PPM.
		Earlier than REV A:
	5496219P259	Ceramic disc: 68 pf ±5%, 500 VDCW, temp coef -80 PPM.
C352	7491827P102	Ceramic disc: .01 µf +80% -30%, 50 VDCW; sim to Sprague 19C180.
C353	5496219P35	Ceramic disc: 4 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C354	5490446P2	Variable, ceramic: approx 5-25 pf, 350 VDCW, temp coef 0 PPM; sim to Erie 557-36.
C355	5496219P158	Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef -30 PPM.
C356	5496219P36	Ceramic disc: 5 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C357	5490446P2	Variable, ceramic: approx 5-25 pf. 350 VDCW,
C358	5496219P158	temp coef 0 PPM; sim to Erie 557-36. Ceramic disc: 62 pf ±5%, 500 VDCW, temp coef
C359	7491827P2	-30 PPM. Ceramic disc: .01 \(\mu f + 80\% - 30\%, \) 50 VDCW; sim
C360	19A115659P1	to Sprague 19C180. Variable: approx 16-141 pf, 150 VDCW; sim to
C361	5496219 P 54	El Menco Type 42. Ceramic disc: 43 pf ±5%, 500 VDCW, temp coef
C362	5496219P13	O PPM. Ceramic disc: 22 pf ±10%, 500 VDCW, temp coef
C363	5490008P19	O PPM. Silver mica: 47 pf ±5%, 500 VDCW; sim to
C364		Electro Motive Type DM-15.
	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C365	19A116080P6	Polyester: .068 μf ±20%, 50 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
C366	5490008P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C367	19A116080P5	Polyester: .047 µf ±20%, 50 VDCW.
C368	19A116080P6	Polyester: .068 µf ±20%, 50 VDCW.
C369	5496267 P 9	Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
C370	7491827P2	Ceramic disc: .01 µf +80%-30%, 50 VDCW; sim to Sprague 19C180.
C371A	5491601P116	Phenolic: 0.62 pf ±5%, 500 VDCW.
C371B	5491601P108	Phenolic: 0.30 pf ±5%, 500 VDCW.
C372	5496219P38	Ceramic disc: 7 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C373	5496219P36	Ceramic disc: 5 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
C374	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C375	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C376A	5496219P243	Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef -80 PPM.
C376B and	5496219P241	Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
C377A C377B	5496219P239	
		coef -80 PPM.
C378	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C379	19A116080P107	Polyester: 0.1 µf ±10%, 50 VDCW.
C381	19A116656P160J1	Ceramic disc: 160 pf ±5%, 500 VDCW, temp coef -150 PPM.
C382	5496219P42	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.
C383	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.
C384	5496219P42	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.
C385	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.
C386	5496219P42	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.
C387	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.
C388	5496219P42	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.
C389	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef
C390	5496219P42	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef 0 PPM.
C391	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.
C392	5496219P42	Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef
C393	19A116656P180J1	O PPM. Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef
C394	5496219P42	-150 PPM. Ceramic disc: 12 pf ±5%, 500 VDCW, temp coef
C395	5490008P34	O PPM. Silver mica: 200 pf ±5%, 500 VDCW; sim to
C396	5494481P128	Ceramic disc: 2700 pf ±10%, 1000 VDCW; sim to
C397	19A116080P1	RMC Type JF Discap. Polyester: .01 µf ±20%, 50 VDCW.
C398	19A116080P5	Polyester: .047 µf ±20%, 50 VDCW.
C399	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to
C401	19A116080P1	RMC Type JF Discap. Polyester: .01 µf ±20%, 50 VDCW.
C402	5490008P119	Silver mica: 47 pf ±10%, 500 VDCW; sim to
C403	5494481P111	Electro Motive Type DM-15. Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to
		RMC Type JF Discap.



(19D415259, Rev. 2) (19D413969, Sh. i, Rev. 4) (19D413909, Sh. i2, Rev. 4)

RESISTANCE READINGS

ALL READINGS ARE MEASURED FROM JACK PINS TO GROUND WITH A BO,000 OHM - PER- VOLT METER, AND WITH ALL EXTERNAL SONNEGTIONS REMOVED. IL OR - SIGNS SHOW METER LEAD GROUNDED.

PIN		1392			ق ل	03	_
NUMBER	eta		METER	+	METER	177	METER SCALE
	INF	INF	XIGGA	300Ω	χιοΩ	325 D	Ωalx
2	INF	INF	×1000	1.7K Q	×IΩ	1.7 K	×IΩ
3	INF	INF	X106₹	3 K 22	-XIQ	INF	X100 D
A	INF	INF	A, Gal X	3.3K Ω	XIU	5 K	XI D
5	9	0	XIΩ	9	XIG	Ø.	Q.IX
ê	INF	INF	XIGGA	INF	χ(100Ω	INF	×100Ω
7	INF	INF	X100A	12 16	RIG	6.5K	×iΩ
8	INF	INF	X1000	INF	X100€	INF	XIGQΩ
9	INF	INF	×10G£	Ą	×10	0	XID.

4301,4303, 4305, 4307, 4369, 431 & 4321

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TERMINAL NUMBERING FOR J304 FLAT

B

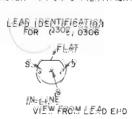
GA

IN-LINE

TRIANGULÁR

VIEW FROM LEAD END

MOTE: LEAD ARRANGEMENT, AND NOT GASE SHABE, IS SETERMINING FACTOR FOR LEAS IDENTIFICATION.



RUNS ON SOLDER SIDE

RUNS ON BOTH SIDES

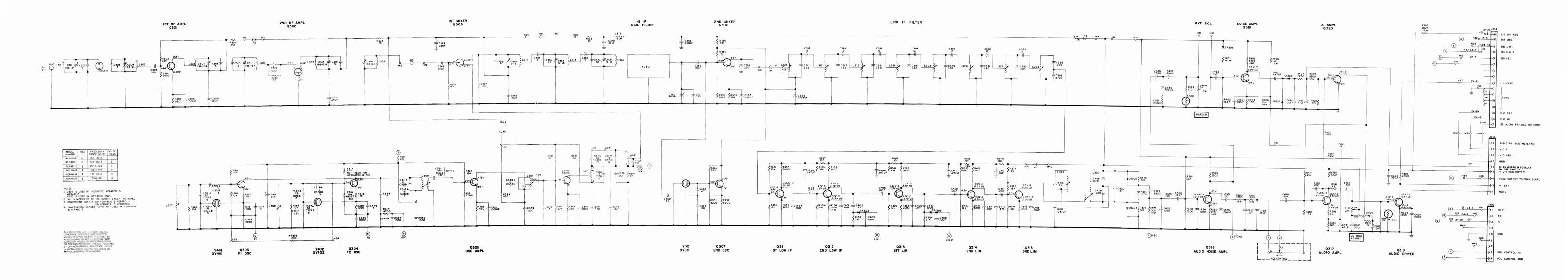
RUNS ON COMPONENT SIDE

OUTLINE DIAGRAM

132—174 MHz RECEIVER MODELS 4ER48C10-15

20

Issue 2



(19R621420, Rev. 9)

SCHEMATIC DIAGRAM

132—174 MHZ RECEIVER MODELS 4ER48C10-15

Issue 2

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T.R.T	-4343
1112 1	-4040

C405 5 C406 1 C407 7 C408 7 C409 5 C410 1 C411 1	19A116080P5 5494481P112 19A116080P1 7491393P1 7491827P2	Polyester: .047 \(\mu f \pm 20\%, \) 50 VDCW. Ceramic disc: 1000 \(\mu f \pm 10\%, \) 1000 VDCW; sim to RMC Type JF Discap. Polyester: .01 \(\mu f \pm 20\%, \) 50 VDCW.	CR304 and									-		
C405 5 C406 1 C407 7 C408 7 C409 5 C410 1 C411 1	5494481P112 19A116080P1 7491393P1	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	and	19A115250P1	Silicon.	Q302	19A115953P1	N channel, field effect.	R333	3R77P682K	Composition: 6800 ohms ±10%, 1/2 w.	R388	3R77P300J	Composition: 30 ohms ±5%, 1/2 w.
C407 7 C408 7 C409 5 C410 1 C411 1	7491393P1	RMC Type JF Discap.	CR305	19411323071	Siffeon.	Q303 and	19A115925P1	Silicon, NPN.	R334	3R77P153K	Composition: 15,000 ohms ±10%, 1/2 w.	R389	3R77P681J	Composition: 680 chms ±5%, 1/2 w.
C407 7 C408 7 C409 5 C410 1 C411 1	7491393P1	Polyester: .01 µf ±20%, 50 VDCW.	CR306	5494922P1	Silicon; sim to Type 1N456.	Q304			R335	3R77P561K	Composition: 560 ohms ±10%, 1/2 w.	R390	3R77P332K	Composition: 3300 ohms $\pm 10\%$, $1/2$ w.
C408 7 C409 5 C410 1 C411 1			CR307	19A115250P1	Silicon.	Q305	19A115342P1	Silicon, NPN.	R336	3R77P331K	Composition: 330 ohms ±10%, 1/2 w.	R391	3R77P431K	Composition: 430 ohms $\pm 10\%$, $1/2$ w.
C409 5 C410 1 C411 1	7491827P2	Ceramic disc: .001 µf +100% -0%, 500 VDCW; sim to Sprague 1219C4.	thru CR309			Q306*	19A116154P1	N channel, field effect.	R337	3R152P333K	Composition: 33,000 ohms ±10%, 1/4 w.	R392(R400)	19B209320P1	Resistor assembly. Variable, carbon film,
C410 1 C411 1		Ceramic disc: .01 µf +80% -30%, 50 VDCW; sim			INDICATING DEVICES		1	In REV A and earlier:	R338	3R152P104K	Composition: 0.10 megohm ±10%, 1/4 w.	11		includes: (R392) 20,000 ohms ±20%, 0.25 w; (R400) 5000 ohms ±20%, 0.25 w:
C410 1 C411 1	5494481P112	to Sprague 19C180. Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	DS301	19B209067P1	Lamp, glow: 0.3 ma; sim to GE NE-2T.		19A115953P1	N channel, field effect.	R339	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.			sim to Centralab Series 5 (Type 71-2).
C411 1	0454401F112	RMC Type JF Discap.				Q307	19A115889P1	Silicon, NPN.	R340*	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.	R393	3R77P392K	Composition: 3900 ohms $\pm 10\%$, $1/2$ w.
	19A116080P1	Polyester: .01 µf ±20%, 50 VDCW.	FL301	19C304219G1	Pandanan 10 7 Min	Q308	19A115245P1	Silicon, NPN.	11		In REV A and earlier:	R394	3R77P103J	Composition: 10,000 ohms $\pm 5\%$, 1/2 w.
0410 -	19A116080P5	Polyester: .047 μf ±20%, 50 VDCW.	11.301	19030421901	Bandpass. 10.7 MHz.	Q309A* and Q309B*	19A115440P1	Silicon, NPN.		3R152P392K	Composition: 3900 ohms ±10%, 1/4 w.	R395	3R77P331K	Composition: 330 ohms ±10%, 1/2 w.
	19A116080P7	Polyester: 0.1 μ f $\pm 20\%$, 50 VDCW.			JACKS AND RECEPTACLES	Q309B*		In REV B, C, D:	R341	3R77P103K	Composition: 10,000 ohms $\pm 10\%$, 1/2 w.	R396 and	19A116278P444	Metal film: 0.28 megohm $\pm 2\%$, $1/2$ w.
C413 5	5494481P108	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	J301	7104941P9	Jack, phono type: phen; sim to Cinch 14H20958.	-	19A115666P1	Silicon, NPN.	R342	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.	R397		
C414 5	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	J302 and	19B209303P1	Connector, phen: 9 pins.			In REV A and earlier:	R343	3R77P331K	Composition: 330 ohms ±10%, 1/2 w.	R399	3R77P471J	Composition: 470 ohms ±5%, 1/2 w.
		RMC Type JF Discap.	J303				19A115342P1	Silicon.	R344	3R77P302J	Composition: 3000 ohms ±5%, 1/2 w.	R400		(See R392).
	19A116080P1	Polyester: .01 μf ±20%, 50 VDCW.	J304	19B205689G2	Connector: 16 contacts.	Q311 thru	19A115889P1	Silicon, NPN.	R345	3R152P623K	Composition: 62,000 ohms ±10%, 1/4 w.	R401	19A116278P357	Metal film: 38,300 ohms ±2%, 1/2 w.
C416 1	19A116656P180J1	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.			INDUCTORS	Q315			R350	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	R402	19A116278P313	Metal film: 13,300 ohms ±2%, 1/2 w.
C417 19	19A116080P5	Polyester: .047 µf ±20%, 50 VDCW.	L301	19B205530G1	Coil,	Q316	19A115123P1	Silicon, NPN; sim to Type 2N2712.	R351	3R77P333K	Composition: 33,000 ohms ±10%, 1/2 w.	R403	3R152P332J	Composition: 3300 ohms ±5%, 1/4 w.
C418 5	5490008P137	Silver mica: 270 pf ±10%, 500 VDCW; sim to	L302	19B205530G2	Coil.	Q317*	19A116774P1	Silicon, NPN; sim to Type 2N5210.	R352 R353	3R77P222K	Composition: 2200 ohms ±10%, 1/2 w.	R404	19A116278P233	Metal film: 2150 ohms ±2%, 1/2 w.
C419		Electro Motive Type DM-15.	L303*	19B205530G2	Coil.			In REV C and earlier:	R353	3R77P562K 3R77P103K	Composition: 10 000 ohms ±10%, 1/2 w.	R405	3R152P153J 3R152P103J	Composition: 15,000 ohms ±5%, 1/4 w.
C420 54	5496219P656	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef			In REV A and earlier:		19A115123P1	Silicon, NPN; sim to Type 2N2712.	R355	3R77P333K	Composition: 10,000 ohms ±10%, 1/2 w. Composition: 33,000 ohms ±10%, 1/2 w.	R400+	3R132P1033	Composition: 10,000 ohms ±5%, 1/4 w. In REV B and earlier:
C421 54	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to		19B205530G6	Coil,	Q318*	19A115300P4	Silicon, NPN; sim to Type 2N3053.	R356	3R152P222K	Composition: 2200 ohms ±10%, 1/2 w.	11	3R152P332J	Composition: 3300 ohms ±5%, 1/4 w.
and C422		RMC Type JF Discap.	L304	19B205530G2	Coil,			In REV C and earlier:	R357	3R77P181K	Composition: 180 ohms ±10%, 1/4 w.	R407	3R77P222K	Composition: 2200 ohms ±10%, 1/2 w.
- 1	9Al16080Pl09	Polyester: 0.22 µf ±10%, 50 VDCW.	L305	19A128122P1	Coil.	0010	19A115300P2	Silicon, NPN; sim to Type 2N3053.	R358	3R77P513J	Composition: 51,000 ohms ±5%, 1/2 w.	R408	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
- 1	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	L306	19A128122P2	Coil.	Q319	19A115889P1	Silicon, NPN.	R359	3R77P562K	Composition: 5600 ohms ±10%, 1/2 w.	R409	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.
		RMC Type JF Discap.	L307 and L308	19A121085G1	Coil. Includes tuning slug 19B200497P2.	Q320	19A115123P1	Silicon, NPN; sim to Type 2N2712.	R360	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	R412	3R77P561K	Composition: 560 ohms ±10%, 1/2 w.
1	.9A116080P6	Polyester: .068 μf ±20%, 50 VDCW.	L309	19B205236G1	Coil Includes turing also lappacetages			RESISTORS	R361	3R77P333K	Composition: 33,000 ohms ±10%, 1/2 w.	R417	3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.
- 1	.9A116080P7	Polyester: 0.1 μf ±20%, 50 VDCW.	L310	19B203236G1	Coil. Includes tuning slug 19B200497P2. Coil. Includes tuning slug 19B200497P2.	R301	3R77P562K	Composition: 5600 ohms $\pm 10\%$, $1/2$ w.	R362	3R77P181K	Composition: 180 ohms $\pm 10\%$, $1/2$ w.	R419	3R77P433J	Composition: 43,000 ohms ±5%, 1/2 w.
and	.9A116080P108	Polyester: 0.15 µf ±10%, 50 VDCW.	L311	19B219059G1	Coil. Includes tuning slug 19B200497P2.	R302	3R77P223K	Composition: 22,000 ohms $\pm 10\%$, $1/2$ w.	R363	3R77P222K	Composition: 2200 ohms ±10%, 1/2 w.	R420	3R77P564J	Composition: 0.56 megohm ±5%, 1/2 w.
C428			L312	19B205224G2	Coil.	R303	3R77P561K	Composition: 560 ohms $\pm 10\%$, $1/2$ w.	R364	3R77P513J	Composition: 51,000 ohms ±5%, 1/2 w.	R421	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
	9A116080P8	Polyester: 0.15 µf ±20%, 50 VDCW.	and L313			R304	3R77P331K	Composition: 330 ohms ±10%, 1/2 w.	R365	3R77P562K	Composition: 5600 ohms ±10%, 1/2 w.	R442*	3R152P331K	Composition: 330 ohms ±10%, 1/4 w. Addied by
C430 54	6494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	L314	19B205224G3	Coil.	R308	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.	R366	3R77P123K	Composition: 12,000 ohms ±10%, 1/2 w.	H .		REV E.
C431 54	496267 P2	Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague	L315	7488079P18	Choke, RF: 15 µh ±10%, 1.2 ohms DC res max;	R309 and	3R77P103K	Composition: 10,000 ohms $\pm 10\%$, 1/2 w.	R367	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.			THERMISTORS
C432 19	9A116080P8	Type 150D.			sim to Jeffers 4421-9K.	R310			R368	3R152P181K	Composition: 180 ohms ±10%, 1/4 w.	RT301	5490828P38	Rod: 1400 ohms ±5%, 1 w max; sim to Globar
l l	494481P14	Polyester: 0.15 µf ±20%, 50 VDCW. Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to	L317	19B219059G2	Coil. Includes tuning slug 19B200497P2.	R311	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.	R369	3R77P512J	Composition: 5100 ohms $\pm 5\%$, $1/2$ w.	RT302	5490828P35	Type 492H. Rod: 3800 ohms ±5%, 1 w max; sim to Globar
,,,,,		RMC Type JF Discap.	L321 and	19A115711P1	Transformer, freq: 455 KHz; sim to Automatic Mfg EX12670.	R312	3R77P150K	Composition: 15 ohms ±10%, 1/2 w.	R370	3R77P181K	Composition: 180 ohms \pm 10%, 1/2 w.	R1302	3490828P33	Type 723B-H.
C435 19	9A116080P203	Polyester: .002 µf ±5%, 50 VDCW.	L322			R313	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	R371	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	11		SOCKETS
C436 19	9C300075P47000J	Polyester: 4700 pf ±5%, 100 VDCW; sim to GE Type 61F.	L323	19A115711P2	Transformer, freq: 455 KHz; sim to Automatic Mfg EX12671.	R314	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.	R372	3R77P333K	Composition: 33,000 ohms ±10%, 1/2 w.	XY401	5490277P1	Transistor, phen: 4 contacts; sim to Elico 3303.
C437 19		Polyester: 3300 pf ±5%, 100 VDCW; sim to	L324	19A115711P1	Transformer, freq: 455 KHz; sim to Automatic	R315 and	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	R373	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.	and XY402		Transferry pion. Techniques, Sin to have 3303.
İ		GE Type 61F.	L325	19A115711P2	Mfg EX12670.	R316	anggreear		R374	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.			
		Polyester: 0.1 µf ±20%, 50 VDCW.	1323	19811571192	Transformer, freq: 455 KHz; sim to Automatic Mfg EX12671.	R317	3R77P682J 3R77P150K	Composition: 6800 ohms ±5%, 1/2 w.	R375 and	3R77P513J	Composition: 51,000 ohms ±5%, 1/2 w.	Y301	19A110215G1	Quartz: freq 10245 KHz, temp range -30°C to
		Polyester: 0.22 µf ±20%, 50 VDCW.	L326	19A115711P1	Transformer, freq: 455 KHz; sim to Automatic Mfg EX12670.	R318 R319	3R77P102K	Composition: 15 ohms ±10%, 1/2 w.	R376					+90°C.
		Polyester: .047 μf ±20%, 50 VDCW.	L327	19Al15711P2	Transformer, freq: 455 KHz; sim to Automatic	R320	3R77P102K 3R77P221K	Composition: 1000 ohms ±10%, 1/2 w. Composition: 220 ohms ±10%, 1/2 w.	R377	3R77P682K	Composition: 6800 ohms $\pm 10\%$, $1/2$ w.	Y401 and	19B206221P1	Quartz: freq range 38.3 to 62 MHz, temp: range -30°C to +80°C. (When reordering give GE Part
		Polyester: 0.1 µf ±20%, 50 VDCW.			Mfg EX12671.	R321*	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.	R378	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.	Y402		Number and specify exact frequency needed). (Crystal frequency = (OF -10.7) : 3).
2443 54		Tantalum: 22 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	L328	19A115711P1	Transformer, freq: 455 KHz; sim to Automatic Mfg EX12670.			In REV A and earlier:	R379	3R77P153K	Composition: 15,000 ohms ±10%, 1/2 w.	11		MICOELI ANEOLIC
2460 54		Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague	L329	19A115711P6	Transformer, freq: 455 KHz; sim to TOKO PEFCN-		3R152P392K	Composition: 3900 ohms ±10%, 1/4 w.	R380	3R77P332J	Composition: 3300 ohms ±5%, 1/2 w.		10412212071	MISCELLANEOUS
461 54		Type 150D. Tantalum: 0.47 μf ±10%, 35 VDCW; sim to			14733-CX12.	R322	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	R381	3R77P333K	Composition: 33,000 ohms ±10%, 1/2 w.	11	19A122139P1 19B205369G1	Cover.
301		Sprague Type 150D.	L330	19A115711P7	Transformer, freq: 455 KHz; sim to TOKO PEFCN-14734-BNL2.	R323	3R77P431J	Composition: 430 ohms ±5%, 1/2 w.	R382	3R152P221J	Composition: 220 ohms ±5%, 1/4 w.		l	Top cover.
162 54	496267P14	Tantalum: 15 μ f \pm 20%, 20 VDCW; sim to Sprague Type 1500.	L331	19B209405P1	Reactor, audio freq: 142 mh ±5% at 0.1 v thru	R324	3R77P101K	Composition: 100 ohms ±10%, 1/2 w.	R383 R384	3R77P332K 3R152P332K	Composition: 3300 ohms ±10%, 1/2 w.		19A121088P1 4035306P62	Can. (Used with L307 and L308).
		oprague Type 1000.			0.27 v; sim to Aladdin 405-101.	R326	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.	R385	l .	Composition: 3300 ohms ±10%, 1/4 w.	11	4036555P1	Washer, fiber. (Used with Y301, FL301).
		DIODES AND RECTIFIERS			TRANSISTORS	R327	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.	R386*	3R152P152K 3R77P163J	Composition: 1500 ohms ±10%, 1/4 w.			Insulator, washer: nylon. (Used with QS18).
R301 77	777146P3	Germanium; sim to Type 1N90.	Q301*	19A116859Pl	Silicon, NPN; sim to Type 2N5032 or 2N3570.	R329	3R152P330K	Composition: 33 ohms ±10%, 1/4 w.	1	JATTELOS	Composition: 16,000 ohms ±5%, 1/2 w. In REV C and earlier:			
R302 40	038056P1	Germanium.			In REV B, C, D:	R330	3R77P333K	Composition: 33,000 ohms ±10%, 1/2 w.		3R77P203J	Composition: 20,000 ohms ±5%, 1/2 w.			
R303				19A115666P1	Silicon, NPN,	R331	3R77P822K	Composition: 8200 ohms ±10%, 1/2 w.		0.1.1.2030	Composition. 20,000 Onms 10%, 1/2 W.			
					In REV A and earlier:	R332	3R77P392K	Composition: 3900 ohms ±10%, 1/2 w.						
				19A115342P1	Silicon, NPN.									

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV. A - Models 4ER48C10-15

REV. B - Incorporated into initial shipment.

REV. C - To improve squelch action. Changed R406.

REV. D - To improve audio at -30°C. Changed Q317, Q318 and R386.

REV. E - To prevent oscillation. Changed Q301 and Q309. Added R422.

(19D41:6517, Rev. 3)

RUNS ON BOTH SIDES

- RUNS ON COMPONENT SIDE

SCHEMATIC & OUTLINE DIAGRAM

SYSTEM BOARD 19C320109G1

PARTS LIST

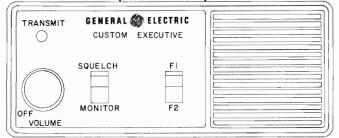
LBI-4351

SYSTEMS BOARD 19C320109G1

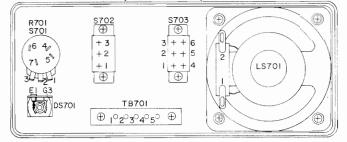
C1	SYMBOL	GE PART NO.	DESCRIPTION
C1 19A116080P101 Polyester: 0.01 µf ±10%, 50 VDCW. C2 5494481P107 Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. C3 and 5496267P2 Tantalum: 47 µf ±20%, 6 VDCW; sim to Sprague Type 150D. C6 5494481P7 Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to Sprague Type 150D. C6 5494481P1 Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C7 5494481P114 Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C8 19A116114P50 Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. C9 5495323P12 Ceramic: .001 µf ±100% =20%, 75 VDCW. C10 19A116080P106 Polyester: 0.068 µf ±10%, 500 VDCW, temp coef -150 PPM. C12 7489162P19 Silver mica: 47 pf ±5%, 500 VDCW; temp coef OPPM. C13 5495323P12 Ceramic: .001 µf ±100% =20%, 75 VDCW.			
C2	C1	19A116080P101	
Sprague Type 150D.	C2	5494481P107	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to
Sprague Type 150D.	and	5496267P2	Tantalum: 47 μ f $\pm 20\%$, 6 VDCW; sim to Sprague Type 150D.
RMC Type JF Discap. Ceramic disc: 2000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic: 39 pf ±5%, 100 VDCW; temp coef -150 PPM. Ceramic: .001 µf +100% -20%, 75 VDCW. Ceramic: .001 µf +100% -20%, 75 VDCW. Cl0 194116080P106 Polyester: 0.068 µf ±10%, 50 VDCW. Cl1 5496219P43 Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef o PPM. Cl2 7489162P19 Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. Cl3 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW.	C5	5496267P11	Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.
RMC Type JF Discap. Ceramic: 39 pf ±5%, 100 VDCW; temp coef -150 PPM. Ceramic: .001 µf +100% -20%, 75 VDCW. Polyester: 0.068 µf ±10%, 50 VDCW. Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef op PM. Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef op PM. C12 7489162P19 Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. C13 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW. INDICATING DEVICES DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES JACKS & RECEPTACLES SINDUCTORS Contact, electrical: sim to Bead Chain L93-3. J33 198205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts. Composition: 5100 ohms ±5%, 1/4 w. Tuning slug. L2 19D402808G35 Coil. L3 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.	C6	5494481P7	
-150 PPM. -150 PPM. -150 PPM. -150 PPM. -150 PPM. -100% -20%, 75 VDCW. -150 PPM. -150	C7	5494481P114	
C10 19A116080P106 Polyester: 0.068 µf ±10%, 50 VDCW. C11 5496219P43 Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef 0 PPM. C12 7489162P19 Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. C13 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW. INDICATING DEVICES DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES Contact, electrical: sim to Bead Chain L93-3. 19B205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts. INDUCTORS L1 19D402808G37 Coil. Includes: Composition: 5100 ohms ±5%, 1/4 w. 5491798P2 Tuning slug. L2 19D402808G35 Coil. Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.	C8	19A116114P50	
C11 5496219P43 Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef 0 PPM. C12 7489162P19 Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15. C13 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW. INDICATING DEVICES DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES Contact, electrical: sim to Bead Chain L93-3. J33 19B205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts. L1 19D402808G37 Coil. Includes: Composition: 5100 ohms ±5%, 1/4 w. Tuning slug. L2 19D402808G35 Coil. Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.	C9	5495323P12	Ceramic: .001 µf +100% -20%, 75 VDCW.
C12 7489162P19 Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C10	19A116080P106	Polyester: 0.068 µf ±10%, 50 VDCW.
Electro Motive Type DM-15. C13 5495323P12 Ceramic: .001 µf +100% -20%, 75 VDCW. INDICATING DEVICES Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES JACKS & RECEPTACLES JACKS & RECEPTACLES Contact, electrical: sim to Bead Chain L93-3. J33 19B205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts. L1 19D402808G37 Coil. Includes: Composition: 5100 ohms ±5%, 1/4 w. 5491798P2 Tuning slug. L2 19D402808G35 Coil. L3 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.	C11	5496219P43	Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef 0 PPM.
DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES J1 thru J32 Contact, electrical: sim to Bead Chain L93-3. J33 19B205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts. INDUCTORS L1 19D402808G37 Coil. Includes: Composition: 5100 ohms ±5%, 1/4 w. 5491798P2 Tuning slug. L2 19D402808G35 Coil. L3 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13. P3 (Part of W2). P101 4029840P2 Contact, electrical: sim to Amp 42827-2. P102 4029840P1 Contact, electrical: sim to Amp 41854.	C12	7489162P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
DS1 4034664P1 Lamp, incandescent: 28 v; sim to GE2148. JACKS & RECEPTACLES J1 thru J32 J33 19B205689G1 Contact, electrical: sim to Bead Chain L93-3. J33 19B205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts.	C13	5495323P12	Ceramic: .001 μf +100% -20%, 75 VDCW.
1			INDICATING DEVICES
J1 thru J32 J33 l9B205689Gl Connector: 16 contacts, includes (16) l9A115853Pl contacts.	DS1	4034664P1	Lamp, incandescent: 28 v; sim to GE2148.
thru J32 J33 19B205689G1 Connector: 16 contacts, includes (16) 19A115853P1 contacts.			JACKS & RECEPTACLES
19Al15853Pl contacts.	thru	4033513P4	Contact, electrical: sim to Bead Chain L93-3.
L1 19D402808G37 Coil. Includes: R15 3R152P512J Composition: 5100 ohms ±5%, 1/4 w. 5491798P2 Tuning slug. L2 19D402808G35 Coil. L3 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.	J33	19B205689G1	Connector: 16 contacts, includes (16) 19All5853Pl contacts.
R15 3R152P512J Composition: 5100 ohms ±5%, 1/4 w. 5491798P2 Tuning slug. L2 19D402808G35 Coil. L3 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.			INDUCTORS
5491798P2 Tuning slug.	L1	19D402808G37	Coil. Includes:
L2 19D402808G35 Coil. Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13.	R15	3R152P512J	Composition: 5100 ohms $\pm 5\%$, $1/4$ w.
L3 7488079P9 Choke, RF: 2.70 µh ±10%, 1.20 ohms DC res max; sim to Jeffers 4411-13%, 1.20 ohms DC res max; sim to Jeffers 4411-13%, 1.20 ohms DC res max; sim to Jeffers 4411-13%, 1.20 ohms DC res max; sim to Jeffers 4411-13%, 1.20 ohms DC res max; sim to Jeffers 4411-13%, 1.20 ohms DC res max; sim to Jeffers 4411-13%, 1.20 ohms DC res max; sim to Wax; sim to Amp 42827-2. P3 (Part of W2). Contact, electrical: sim to Amp 42827-2. Contact, electrical: sim to Amp 41854.		5491798P2	Tuning slug.
Sim to Jeffers 4411-13.	L2	19D402808G35	Coil.
P3 (Part of W2). P101 4029840P2 Contact, electrical: sim to Amp 42827-2. P102 4029840P1 Contact, electrical: sim to AMP 41854.	L3	7488079 P 9	Choke, RF: 2.70 μh $\pm 10\%$, 1.20 ohms DC res max; sim to Jeffers 4411-13.
P101 4029840P2 Contact, electrical: sim to Amp 42827-2. P102 4029840P1 Contact, electrical: sim to AMP 41854.			
P102 4029840P1 Contact, electrical: sim to AMP 41854.	Р3		(Part of W2).
	P101	4029840P2	Contact, electrical: sim to Amp 42827-2.
Q1 19A115123P1 Silicon, NPN; sim to Type 2N2712. Q2 19A116016P1 Silicon, NPN.	P102	4029840Pl	
Q2 19A116016P1 Silicon, NPN.			
RESISTORS RESISTORS RESISTORS RESISTORS RESISTORS RESISTORS RESISTORS RESISTORS			
R1 19B209022P25 Wirewound: 2.7 ohms ±5%, 2 w; sim to IRC Type BWH. R2 19A116559P110 Variable, cermet: 50 ohms ±20%, 1/2 w; sim to CTS Series 360.	Q2	19A116016P1	
R2 l9Al16559Pl10 Variable, cermet: 50 ohms $\pm 20\%$, $1/2$ w; sim to CTS Series 360.	R1	19B209022P25	Wirewound: 2.7 ohms ±5%, 2 w; sim to IRC
	R2	19Al16559P110	Variable, cermet: 50 ohms ±20%, 1/2 w; sim to
	R3	3R77P270J	

SYMBOL	GE PART NO.	DESCRIPTION
R4	3R78P331J	Composition: 330 ohms ±5%, 1 w.
R5 and R6	19B209022P89	Wirewound: 0.1 ohms ±5%, 2 w; sim to IRC Type BWH.
R7	3R77P680J	Composition: 68 ohms ±5%, 1/2 w.
R8	3R77P302J	Composition: 3000 ohms ±5%, 1/2 w.
R9	3R77P101J	Composition: 100 ohms ±5%, 1/2 w.
R10	19B209358P106	Variable, carbon film: approx 75 to 10,000 ohms ±10%, 0.25 w; sim to CTS Type X-201.
R11	19B209022P15	Wirewound: 1.0 ohms $\pm 5\%$, 2 w; sim to IRC Type BWH.
R12	3R77P120J	Composition: 12 ohms ±5%, 1/2 w.
R13 and R14	3R77P473J	Composition: 47,000 ohms ±5%, 1/2 w.
R16	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.
VR1	4036887D6	
AKI	4036887P6	Silicon, Zener.
147	1000000000	
Wl	19B209044P19	RF: approx 6 inches; sim to Times M1-5280.
W2	19B219584G1	RF: approx il inches long.
	19A121252P1	Heat sink. (Used with Q2).
	4029006P3	Clip, compression: 0.375 x 0.19 x .02 inches; sim to Tinnerman C5426-014-24. (Used with Q2).
	400055577	
	4036555P1	Insulator, washer: nylon. (Used with Q2).
	4035711P4	Clip, spring tension: sim to Augat Bros. 6007-8-CT. (Used with DS1).
	19B201074P216	Screw, tap: No. 6-32. (Secures J33).

CONTROL UNIT (FRONT VIEW)



CONTROL UNIT (REAR VIEW)

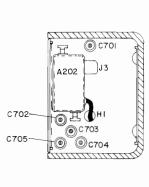


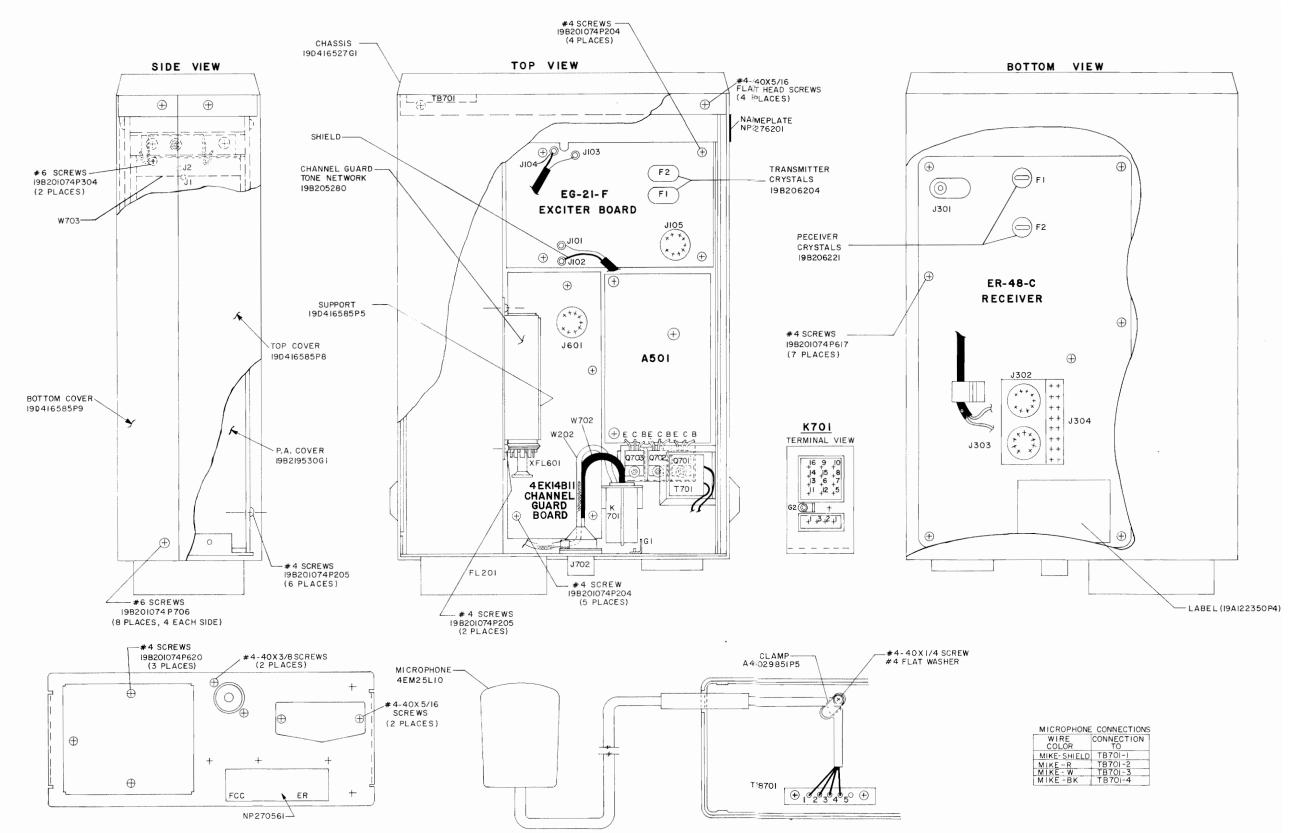
NOTE

- I. PART OF HARDWARE KIT FURNISHED WITH PLI9D416527GI.
- 2. PART OF HARDWARE KIT FURNISHED WITH 4EKI4BII.
- 3. TONE NETWORK TO BE ORIENTED SO MARKING APPEARS ON THIS SURFACE.
- 4. SPOT TIE P601 TO HARNESS IF CHANNEL GUARD OPTION NOT REQ'D.

OUTLINE DIAGRAM

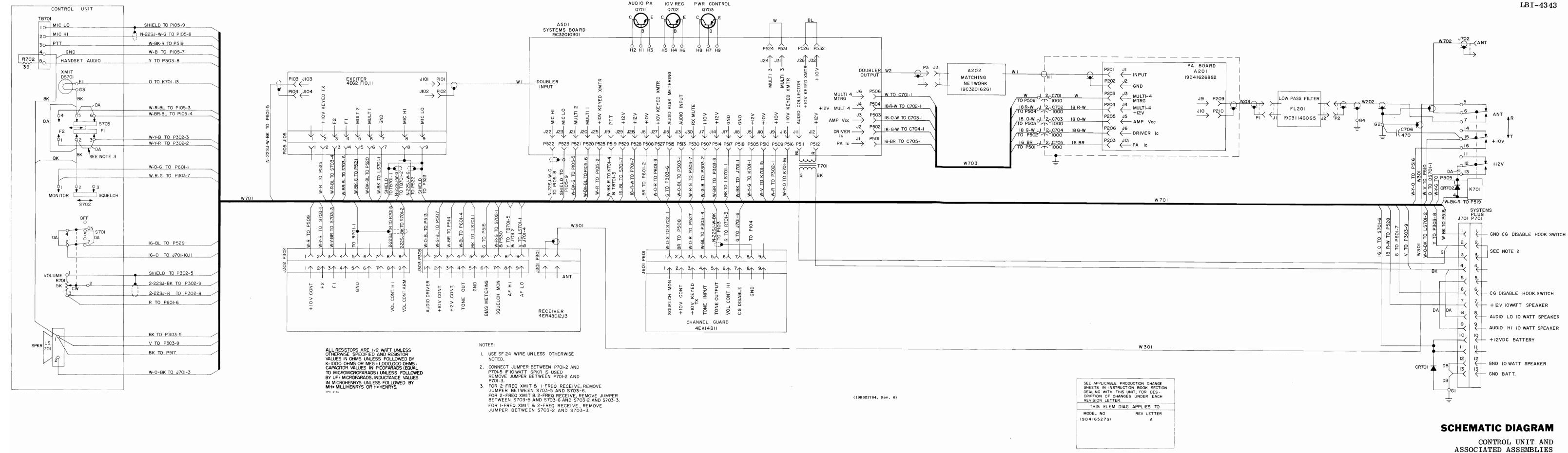
CONTROL UNIT AND ASSOCIATED ASSEMBLIES





VIEW AT "A"

(19R621860, Rev. 2)



PARTS LIST

LBI-4352B CONTROL UNIT/SYSTEM 19D416527G1

RMC Type JF Discap. DIODES AND RECTIFIERS Silicon. Silicon. Silicon. 1901 193115823P1 Silicon. INDICATING DEVICES Socket, pinen: 13 contacts rated at amps max. JACKS AND RECEPTACLES Socket, pinen: 13 contacts rated at amps max. LOUDSPEAKERS Socket, pinen: 13 contacts rated at amps max.	SYMBOL	GE PART NO.	DESCRIPTION
S494481P7 Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to Galdan. Ceramic disc: 470 pf ±20%, 1000 VDC			
RMC Type JF Discap. DIODES AND RECTIFIERS Silicon. Silicon. Silicon. 1901 193115823P1 Silicon. INDICATING DEVICES Socket, pinen: 13 contacts rated at amps max. JACKS AND RECEPTACLES Socket, pinen: 13 contacts rated at amps max. LOUDSPEAKERS Socket, pinen: 13 contacts rated at amps max.			
Silicon Sili	C706	5494481P7	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
			DIODES AND RECTIFIERS
19701 4034664P1 Lamp, incandescent: 28 v; sim to GE2148.	CR701	19A115823P1	Silicon.
	CR702	4037822P2	Silicon.
19C303576P1 Socket, phen: 13 contacts rated at amps max.			
19C303576P1 Socket, phen: 13 contacts rated at amps max.	D\$701	4034664P1	Lamp, incandescent: 28 v; sim to GE2148.
19C303576P1 Socket, phen: 13 contacts rated at amps max.			JACKS AND DECEDTACLES
19A116701P1 Permanent magnet: 3 inch, 3.2 ohms ±10% voice coil imp, freq range to 1000 Hz; sim to Oaktron 3A3C.	J701	19C3O3576P1	
Permanent magnet: 3 inch, 3.2 ohms ±10% voice coil imp, freq range to 1000 Hz; sim to Oaktron 3A3C.]
voice coil imp, freq range to 1000 Hz; sim to Oaktron 3ASC.			
103 4029840P2 Contact, electrical: sim to Amp 42827-2. 104 4029840P1 Socket, tube: 9 pins; sim to Elco 04-920-XX. 105 19B209341P2 Socket, tube: 9 pins; sim to Elco 04-920-XX. 106 4029840P2 Contact, electrical: sim to Amp 42827-2. 107 4029840P2 Contact, electrical: sim to Amp 42827-2. 108 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P1 Contact, electrical: sim to Amp 42827-2. 109 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P1 Contact, electrical: sim to Amp 42827-2. 109 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P3 Contact, electrical: sim to Amp 42827-2. 108 4029840P3 Contact, electrical: sim to Amp 42827-2. 109 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P3 Contact, electrical: sim to Amp 42827-2. 109 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P3	LS701	19A116701P1	Permanent magnet: 3 inch, 3.2 ohms ±10% voice coil imp, freq range to 1000 Hz; sim to Oaktron 3A3C.
Contact, electrical: sim to AMP 41854. Contact, electrical: sim to AMP 41854. Socket, tube: 9 pins; sim to Elco 04-920-XX. Socket, tube: 9 pins; sim to Elco 04-920-XX. Contact, electrical: sim to Amp 42827-2. Contact, electrical: sim to Amp 42827-3. Contact, electrical: sim t			
19B209341P2 Socket, tube: 9 pins; sim to Elco 04-920-XX. 19B209341P2 Socket, tube: 9 pins; sim to Elco 04-920-XX. 19B209341P2 Socket, tube: 9 pins; sim to Elco 04-920-XX. 105 4029840P2 Contact, electrical: sim to Amp 42827-2. 107 4029840P2 Contact, electrical: sim to Amp 42827-2. 108 4029840P2 Contact, electrical: sim to Amp 42827-2. 109 4029840P1 Contact, electrical: sim to AMP 41854. 109 4029840P2 Contact, electrical: sim to AMP 41854. 109 4029840P1 Contact, electrical: sim to AMP 41854. 109 4029840P1 Contact, electrical: sim to AMP 41854. 109 4029840P2 Contact, electrical: sim to AMP 42827-2. 109 4029840P3 Contact, electrical: sim to AMP 42827-2. 100 4029840P2 Contact, electrical: sim to AMP 42827-2. 101 4029840P2 Contact, electrical: sim to AMP 42827-2. 102 4029840P2 Contact, electrical: sim to AMP 42827-2. 103 4029840P2 Contact, electrical: sim to AMP 42827-2. 104 4029840P2 Contact, electrical: sim to AMP 42827-2. 105 4029840P2 Contact, electrical: sim to AMP 42827-2. 106 4029840P2 Contact, electrical: sim to AMP 42827-2. 107 5496870P13 Resistor/Switch: variable, carbon film: 5000 ohms: ±20%: switch: DPST, 6 amps at 125 VAC; sim to Mallory LC(5K)OAC-2. 100	P103	4029840P2	Contact, electrical: sim to Amp 42827-2.
19B209341P2 Socket, tube: 9 pins; sim to Elco 04-920-XX. 105 d029840P2 Contact, electrical: sim to Amp 42827-2. 107 d029840P2 Contact, electrical: sim to Amp 42827-2. 108 d13 d19 d029840P2 Contact, electrical: sim to Amp 42827-2. 109 d19 d029840P1 Contact, electrical: sim to AMP 41854. 109 d029840P2 Contact, electrical: sim to AMP 41854. 109 d029840P2 Contact, electrical: sim to AMP 41854. 109 d029840P1 Contact, electrical: sim to AMP 41854. 109 d029840P1 Contact, electrical: sim to AMP 42827-2. 100 d029840P2 Contact, electrical: sim to AMP 42827-2. 101 d029840P2 Contact, electrical: sim to AMP 42827-2. 1028 d029840P3 Contact, electrical: sim to AMP 42101-2. 1030 d029840P2 Contact, electrical: sim to AMP 42101-2. 1040 d029840P2 Contact, electrical: sim to AMP 42827-2. 1051 d029840P2 Contact, electrical: sim to AMP 42827-2. 1052 d030 d030 d030 d030 d030 d030 d030 d03	104	4029840P1	Contact, electrical: sim to AMP 41854.
	105	19B209341P2	Socket, tube: 9 pins; sim to Elco 04-920-XX.
Contact, electrical: sim to Amp 42827-2. 103 4029840P2 Contact, electrical: sim to Amp 42827-2. 104 105 107 108 109 4029840P1 Contact, electrical: sim to AMP 41854. 109 109 100 100 100 100 100 100 100 100	302 nd 303	19B209341P2	Socket, tube: 9 pins; sim to Elco 04-920-XX.
Tru 100 4029840P2	505	4029840P2	Contact, electrical: sim to Amp 42827-2.
18	507 hru 510	4029840P2	Contact, electrical: sim to Amp 42827-2.
Contact, electrical: sim to Amp 42827-2. 4029840P1	P513 thru P518	4029840P2	Contact, electrical: sim to Amp 42827-2.
1922 1923 1924 1929 1929 1920 1920 1921 1922 1922 1922	P519	4029840P1	Contact, electrical: sim to AMP 41854.
Contact, electrical: sim to Amp 42827-2. 228 4029840P3 Contact, electrical: sim to AMP 42101-2. 329 330 4029840P2 Contact, electrical: sim to AMP 42827-2. 331 332 332 331 332 332 333 333 334 335 336 337 338 339 339 330 330 4029840P2 Contact, electrical: sim to Amp 42827-2. 331 332 332 333 333 334 335 335 336 337 338 338 338 338 338 338 338 338 338	P520 thru P522	4029840P2	Contact, electrical: sim to Amp 42827-2.
128 4029840P3 Contact, electrical: sim to AMP 42101-2.	P5 23	4029840P1	Contact, electrical: sim to AMP 41854.
Contact, electrical: sim to AMP 42101-2. do	P524 thru P527	4029840P2	Contact, electrical: sim to Amp 42827-2.
Contact, electrical: sim to Amp 42827-2. 198209341P2	P528 and P529	4029840P3	Contact, electrical: sim to AMP 42101-2.
Socket, tube: 9 pins; sim to Elco 04-920-XX.	P530 thru P532	4029840P2	Contact, electrical: sim to Amp 42827-2.
Resistor/Switch: variable, carbon film: 5000 ohms ±20%; switch: DPST, 6 amps at 125 VAC; sim to Mallory LC(5K)OAC-2.	P601	19B209341P2	Socket, tube: 9 pins; sim to Elco 04-920-XX.
ohms ±20%; switch: DPST, 6 amps at 125 VAC; sim to Mallory LC(5K)OAC-2.			RESISTORS
	R701	5496870P13	ohms ±20%; switch: DPST, 6 amps at 125 VAC;
(Part of R701).			SWITCHES
	S701		(Part of R701).
l l			

SYMBOL GE PART NO.		DESCRIPTION	
S702	19A116622P3	Push: DPDT, .5 amp at 125 VDC/VAC, 2 amps at 14 VDC res max; sim to Switchcraft 51206LH.	
S703	19A116622P2	Push: DPDT, .5 amp at 125 VDC/VAC, 2 amps at 14 VDC res max; sim to Switchcraft 51206LH.	
TB701	19A129242G1	TERMINAL BOARDS Terminal board: 5 contacts.	
W202	19A129265P1	RF: approx 6 inches long.	
W301	19A129262P1	BE: approx 21 inches long	
W701	19B219518G1	RF: approx 21 inches long. System Cable. Includes C706, CR701, CR702, J701, P103-P105, P302, P303, P505, P507-P510, P513-P532, P601, R701, R702, S701-S703, TB701, W202, W301, W702, and XK701.	
W702	19A122133G14	Antenna jack: approx 5 inches long. Includes (J702).	
XK701	5491595 <i>2</i> 5	Relay: 16 contacts; sim to Allied Control 30054-2.	
	19A129240G1	MISCELLANEOUS Support. (Used with DS701).	
	4031053P7	Nut, sheet spring; sim to Tinnerman Cl2046- 012-67. (Used to secure LS701).	
	N402P5C6	Flatwasher: No. 4. (Used to secure LS701).	
	19A122138P1	Knob. (Used with Pl05, P302, P303, and P601).	
	N197P408C6	Wood screw: steel, No. 4, 1/2" long. (Used with Pl05, P302, P303, and P601).	
	7115130P9	Lockwasher: sim to Shakeproof 1220-2. (Used with R701-S701).	
	7165075P2	Hex nut, brass: No. 3/8-32. (Used with R701- S701).	
	19B201074P205	Screw, Phillips Pozidriv: 4-40-5/16. (Secures TB701).	
	19A129260P1	Support. (Used with XK701).	
	5491595P10	Retainer: spring; sim to Allied Control 30052-1. (Used with XK701).	
	19D416585P1	Control head case.	
	NP270664	Nameplate.	
	19A129244G1	Knob. (VOLUME).	
	19B204949P1	Jewel: red plastic lens. (TRANSMIT).	
		SYSTEM	
		FILTERS	
FL201	19C311460G5	Lowpass.	
K 701	19C307010P18	Armature: 12 VDC nominal, 1.5 w max operating, 130 ohms ±10% coil res, 4 form C contacts; sim to Allied Control T154-X-976A.	
P511 and	4029840P2		
P512		TRANSISTORS	
Q701	19A116742P1	Silicon, NPN.	
Q702	19A116118P1	Silicon, NPN.	
Q703	19A116375P1	Silicon, PNP.	
т701	19B209079P1	Audio freq: 0.3-3 KHz freq range, Pri: 55 ohms ±10% imp, 0.895 ohm ±10% DC res, Sec: 3.2 ohms imp, 0.168 ohm DC res.	

		DESCRIPTION
W201		CABLE ASSEMBLY 19A129263G1
P209	4029840P2	Contact, electrical: sim to Amp 42827-2.
P210	4029840P1	Contact, electrical: sim to AMP 41854.
W703		CABLE ASSEMBLY 19A129238G1
		CAPACITORS
C701 thru C705	5493392P7	Ceramic, feed-thru: 1000 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FA5C.
P203	4029840P2	Contact, electrical: sim to Amp 42827-2.
P204 and P205	4029840P3	Contact, electrical: sim to Amp 42101-2.
P206	19B209151P1	Terminal, solderless: sim to Amp 42284-5.
P213	19B209151P1	Terminal, solderless: sim to Amp 42284-5.
P501 thru P504	4029840P3	Contact, electrical: sim to Amp 42101-2.
P506	4029840P2	Contact, electrical: sim to Amp 42827-2.
		ASSOCIATED ASSEMBLIES
		POWER CABLE ASSEMBLY 19A129305G1
		MISCELLANEOUS
	19A121322G1	Lead: approx 9 feet long.

7484390P4 Fuse, quick blowing: 8 amp 250 v; sim to Littel-fuse 31408 or Bussmann ABC-08. 19A121324G2

19A121441G1 Vehicle Systems Plug. 19C3O3574P1 4033204P5

7878455P2

5491595P9

N44P9006C13 Screw: No. $4 \times 1/32$, (Secures Vehicle Systems Plug to cover). 19A121167P1 Screw: .750 dia. (Secures connector to radio).

ANTENNA - 4EY12A13 150.8-174 MHz

	MISCELLANEOUS
19B201074P204	Tap screw, Phillips Pozidriv: No. 4-40 x 1/4. (Secures A501).
19D416585P4	Backplate, (Locates FL201 and J701).
19B219474P1	Cover. (Used with FL201).
19A127181P1	Plate. (Used with FL201).

19B201074P620 Tap screw: No. $4-40 \times 1-1/4$. (Secures cover to FL201). Solderless terminal. (Used with J701). Retainer: spring; sim to Allied Control 30040-2. (Used with K701).

19A116023P1 Insulator plate. (Used with Q701-Q703). N402P55P6 Washer: No. 6. (Used with Q701-Q703). 19A129318P1 Plate. (Used with Q701-Q703).

DESCRIPTION GE PART NO.

7160861P27 Nut, sheet spring: sim to Tinnerman. (Secures T701). 7878455Pl Solderless terminal. (Used with W202). 19B209209P205 Tap screw: N. 4-40 x 5/16. (Secures Control Head to Chassis). 19B201074P305 Screw, tap: No. 6-32 x 5/16. (Secures Backplate to frame).

SYMBOL

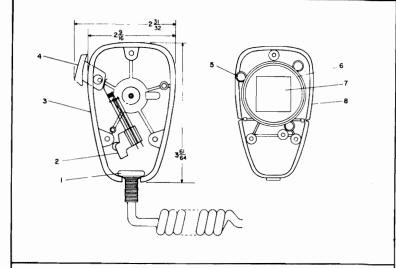
4038050P4

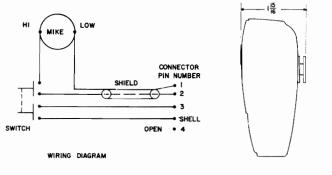
Cap screw: thread size 10-32 UNF2A. (Secures PA Board to channel).

MILITARY MICROPHONE MODEL 4EM25L10

PARTS LIST

SYMBOL	GE PART NO.	DESCRIPTION
1		Cable clamp, front and back case. Shure Brothers RP897.
2		Switch. Shure Brothers RP26.
3		Case, back. (See item 1).
4		Switch button. Shure Brothers RP97. (Quantity 5 only).
5	l	Spring and internal hardware. Shure Brother's RP16.
6		Shield. Shure Brothers RP23. (Quantity 5 conly).
7		Magnetic controlled cartridge, grille cloth, screen and resonator. Shure Brothers RP13.
8		Case, front. (See item 1).
9		Cable: approx 6 feet long, includes (4) 4029840Pl female terminals. Shure Brothers RP786.





-MILITARY MICROPHONE-

PA TRANSISTOR REPLACEMENT

-WARNING -

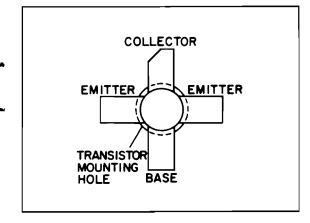
The stud mounted RF Power Transistors used in the transmitter contain Berryllium Oxide, a TOXIC substance. If the ceramic or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors of this type.

To replace the PA transistors (Q1 through Q4):

- 1. Unsolder one lead at a time with a 50-Watt soldering iron. Use a scribe to hold the lead away from the printed circuit board until the solder cools.
- 2. Remove the PA Assembly as directed in the Disassembly Procedure (see Table of Contents).
- 3. Hold the body of the transistor to prevent it from turning. Next, remove the transistor hold-down nut and springwasher through the hole in the heatsink with an 11/32-inch nut-driver. Lift out the transistor, and remove the old solder from the printed circuit board.
- 4. Trim the new transistor leads (if required) to approximately 3/8-inch lengths. Cut the collector lead at a 45° angle for future identification (see Figure 1). The letter "C" on the top of the transistor indicates the collector.
- 5. Apply a coating of silicon grease around the transistor mounting surface, and place the transistor in the mounting hole. Align the leads as shown in the Outline Diagram. Then hold the body of the transistor and replace the hold-down nut and spring washer, using moderate torque (6.5 inch-pounds for 150.8 to 470 MHz transmitters).
- 6. Make sure that the transistor is mounted as shown in Figure 2 so that the leads can be soldered to the printed curcuit pattern, starting from the inner edge of the mounting hole.
- 7. Solder the leads to the printed circuit pattern. Start at the inner edge of mounting hole and solder the remaining length of transistor lead to the board.

-CAUTION-

Failure to solder the transistor leads as directed may result in the generation of RF loops that could damage the transistor.



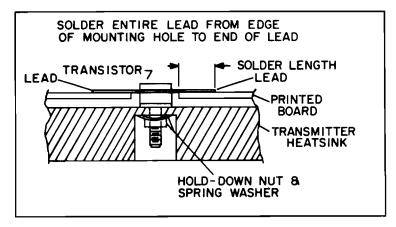


Figure 1 - Lead Identification

Figure 2 - Transistor Mounting

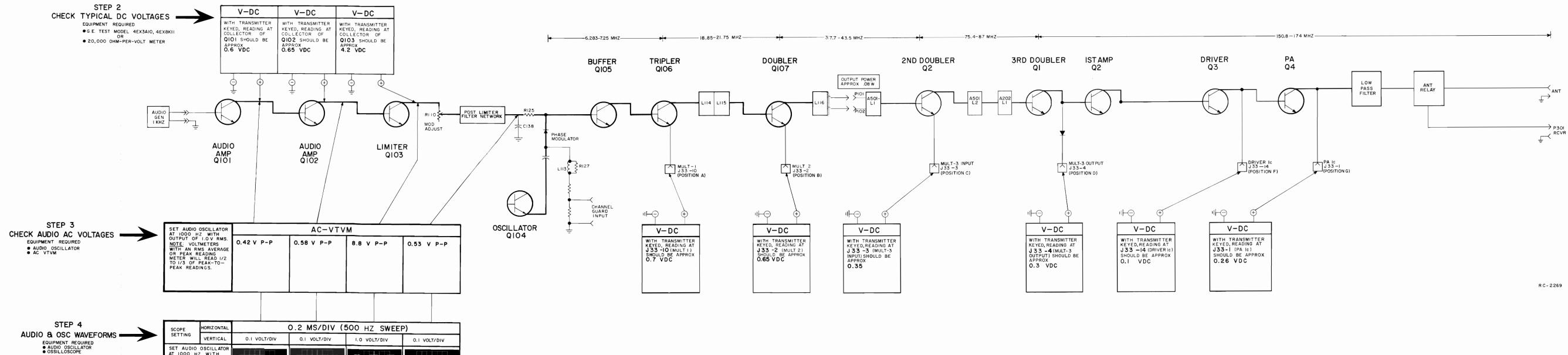
	Probable Defective Stage		
Meter Position	High Meter Reading	Low Meter Reading	Zero Meter Reading
A (MULT-1)	Q105 or Q106	Q105 or open L113	10-Volt regulator, osc. crystal or Q104, Q105, Q106
B (MULT-2)	Q107, A201-Q1	Q107	Q107
C (MULT-3) INPUT	A201-Q1	10-Volt regu- lator, A201- Q1	10-Volt regu- lator, A201-Q1
D (MULT-3) OUTPUT	A202-Q2	13.1 Volts A202-Q1	13.1 Volts A202-Q1
F (DRIVER Ic)	A202-Q4	Q3, or pro- tective cir- cuits acti- vated*	Keyed 12 Volts, A202-Q2, Q3
G (PA Ic)	Mis-aligned PA. Check Step 7 of Alignment Procedure.	Q4 or pro- tective cir- cuits activated*	Keyed 12 Volts, A202-Q4

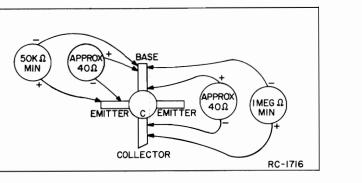
* Refer to the power regulator Troubleshooting Procedure for check of protective circuit.

PA TRANSISTOR CHECKS

PA transistors Q1 thru Q4 can be checked to determine if they are defective by measuring the junction resistances with an ohmmeter according to the following procedure:

- 1. Unsolder the base and collector leads with a 50-Watt soldering iron. Use a scribe to hold each lead off the printed circuit board until the solder cools.
- 2. Slip a piece of paper under each unsoldered lead to insulate it from the printed circuit board.
- 3. Measure the base-to-emitter and base-to-collector resistances. and check with the "good" resistance readings as shown in RC-1716. Always take two different readings for each junction by reversing the meter leads.
- 4. If replacement of a transistor is necessary, refer to the replacement procedure listed in the Table of Contents.





SET AUDIO OSCILLATOR AT 1000 HZ WITH OUTPUT OF 1.0 V RMS.

TROUBLESHOOTING PROCEDURE

TRANSMITTER TYPE KT-25-A

Issue 1

LBI-4343

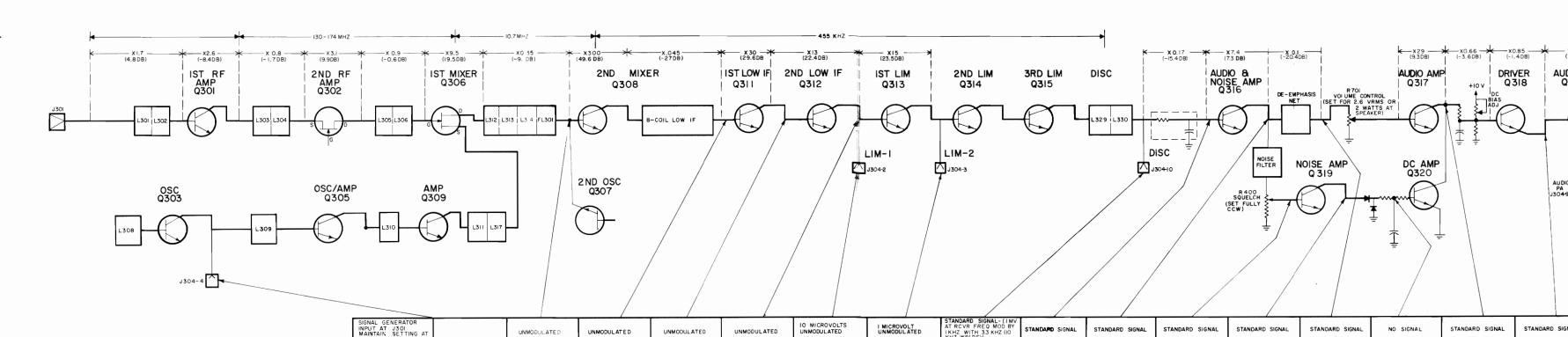
STEP I - QUICK CHECKS

SYMPTOM	PROCEDURE
NO SUPPLY VOLTAGE	Check power connections and continuity of supply leads, and check fuses. If fuse is blown, check for short circuits by disconnecting all plugs in the unit. Reconnect plugs one at a time until a fuse blows.
NO REGULATED 10 VOLTS	Check the 12-Volt supply. Then check Q1 and Q702 in 10-Volt regulator and regulator circuit. Disconnect all plugs from the receiver, exciter board and option boards, and take resistance readings from jack pins to ground (Refer to Outline Diagrams).
LOW 2ND LIM READING	Check supply voltages and then check oscillator reading at J304-4 as shown in STEP 2A.
	Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 2nd Limiter stages as shown in STEP 2A.
	Check receiver RF alignment (refer to Receiver Alignment Procedure).
LOW OSCILLATOR READING	Check alignment of Oscillator (Refer to Front End Alignment Procedure).
	Check voltage readings of Q304 and Q305. Check resistance readings on J302-1, -2 and -3.
	Check crystal ¥401.
LOW RECEIVER SENSITIVITY	Check Front End Alignment (Refer to Front End Alignment Procedure).
	Check input signal required for 0.2-Volt reading at LIM-1. Reading should be less than 20 uv.
	Check antenna connections, cable and relay.
	Check voltage readings of 1st and 2nd RF Amps and 1st and 2nd Mixers.
	Make SIMPLIFIED GAIN CHECKS (STEP 2A).
NO AUDIO	Check jumper connections on power cable.
LOW AUDIO	Check Audio PA (Q701) output current at J304-9. If reading is low
	 a. Check BIAS ADJ for 0.25 VDC at J304-9. If incorrect, set for 0.25 V with R392 (Position G on Test Set).
	b. If correct, check Audio Amp Q317.
	Make SIMPLIFIED GAIN and WAVEFORM CHECKS (STEPS 2A and 2B) of Audio and Squelch Stages.
	Check unsquelched D-C voltage readings in Audio section (Refer to Receiver Service Sheet).
	Check voltage readings on Channel Guard receiver.
	Check setting of SQUELCH control R400 (Refer to Receiver Alignment Procedure).
IMPROPER SQUELCH OPERATION	Make GAIN and WAVEFORM CHECKS (STEPS 2A and 2B) of Audio and Squelch stages.
DISCRIMINATOR IDLING TOO FAR OFF ZERO	See if discriminator zero is in the center of IF bandpass.

TROUBLESHOOTING PROCEDURE

RECEIVER MODELS 4ER48C10-15

32Issue 1



UNMODULATED

IO MICROVOLTS UNMODULATED

I MICROVOLT UNMODULATED

EQUIPMENT REQUIRED:

STEP 3- GAIN-PER-STAGE

AMP FACTOR

EQUIPMENT REQUIRED:

PROCEDURE

READINGS-

RF VOLTMETER (SIMILIAR TO BOONTON MODEL 91-CA OR MILLIVAC TYPE MV-18 C.

SIGNAL ON RECEIVER FREQUENCY (BELOW SATURATION). CORRECT FREQUENCY CAN BE DETERMINED BY ZEROING THE DISCRIMINATOR.

i. APPLY PROBE TO INPUT OF STAGE (FOR EXAMPLE, BASE OF RF AMP). PEAK RESONANT CIRCUIT OF STAGE BEING MEASURED AND TAKE VOLTAGE READING (E₁).

2. MOVE PROBE TO INPUT OF FOLLOWING STAGE (IST MIXER \Re . REPEAK FIRST RESONANT CIRCUIT THEN PEAK CIRCUIT BEING MEASURED AND TAKE READING (E $_2$).

CONVERT READINGS (BY SUBTRACTING E, FROM E₂ ON THE DB SCALE OF RF VOLTMETER, OR) BY MEANS OF THE FOLLOWING FORMULA.

4. CHECK RESULTS WITH TYPICAL GAINS SHOWN ON DIAGRAM BELOW. 5. USE PROCEDURE LISTED ABOVE TO FIND GAIN OF EACH STAGE. ★ NOTE: REMOVE CRYSTAL OR SHORT OUT OSC. BASE BEFORE MEASURING MIXER STAGES TO ELIMINATE INJECTION VOLTAGE

I. VTVM-AC&DC

STEP 2A- SIMPLIFIED VTVM

2. SIGNAL GENERATOR (MEASUREMENTS M560 EQUIV.)

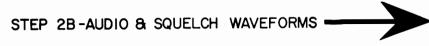
PRELIMINARY STEPS:

SET VOLUME CONTROL FULLY CLOCKWISE.

2. SET SQUELCH CONTROL FULLY COUNTERCLOCKWISE.

3. RECEIVER SHOULD BE PROPERLY ALIGNED.

GAIN CHECKS



UNMODULATED

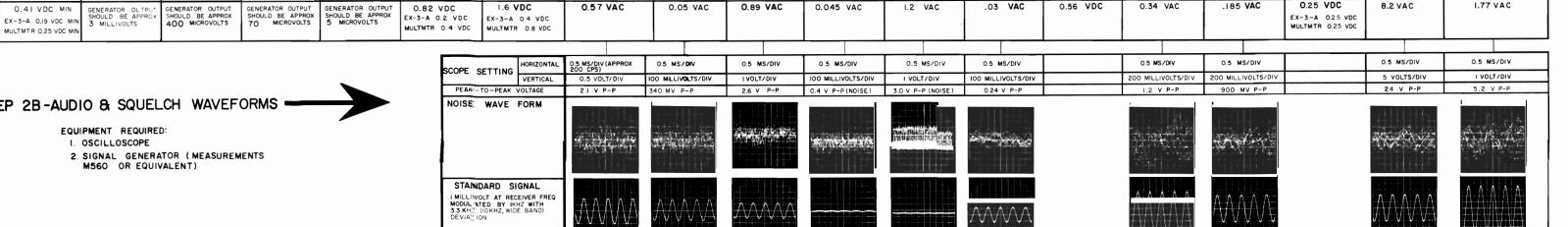
UNMODULATED

EQUIPMENT REQUIRED: I. OSCILLOSCOPE

UNMODULATED

READING

2. SIGNAL GENERATOR (MEASUREMENTS M560 OR EQUIVALENT)



STANDARD SIGNAL

NO SIGNAL

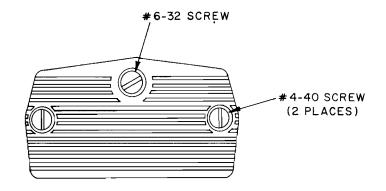
STANDARD SIGNAL

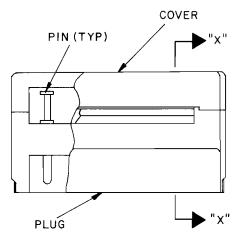
STANDARD SIGNAL STANDARD SIGNAL

NO SIGNAL

STANDARD SIGNAL

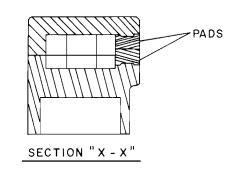
DISCONNECT LS701 WHEN USING A 3.2-OHM EXTERNAL LOAD.





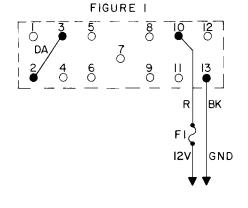
INSTALLATION INSTRUCTIONS

- I. ASSEMBLE PINS IN PROPER HOLES.
- 2. ASSEMBLE COVER TO PLUG MAKING SURE LEADS LAY IN A SINGLE ROW AT CABLE ACCESS SLOT.
- 3. WHEN SOLDERING AN ADDITIONAL WIRE TO AN EXISTING PIN (AS IN HANDSET HOOKSWITCH) HOLD WIRE AND SOLDER BUILDUP TO A MINIMUM TO PREVENT SHORT CIRCUITS.
- 4. ASSEMBLE PADS IN APPROXIMATE POSITIONS SHOWN.

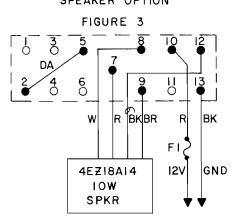


12V NEGATIVE GROUND

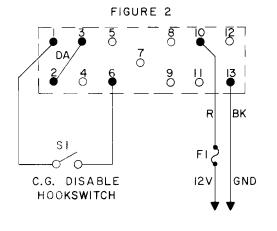
STANDARD CABLE



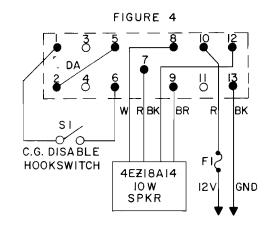
STANDARD CABLE WITH IOW SPEAKER OPTION



STANDARD CABLE WITH C.G. HOOKSWITCH OPTION



STANDARD CABLE WITH IOW SPEAKER OPTION AND C.G., HOOKSWITCH OPTION



(19C320195, Rev. 3)

SYSTEM PLUG CONNECTIONS

This modification for 132-174 MHz receivers Type ER-48-C reduces the susceptibility of the receiver to intermodulation interference by decreasing the receiver sensitivity.

PROCEDURE

- 1. Remove the top cover from the receiver.
- 2. Unsolder the lead of capacitor C305 (see Figure 1) and solder one lead of a 39-ohm, 5%, 1/4-watt resistor (GE Part No. 3R152P390J) into the hole from which the capacitor lead was removed.
- 3. Solder the other lead of the resistor and capacitor together as shown in View "A".
- 4. Replace the top cover.

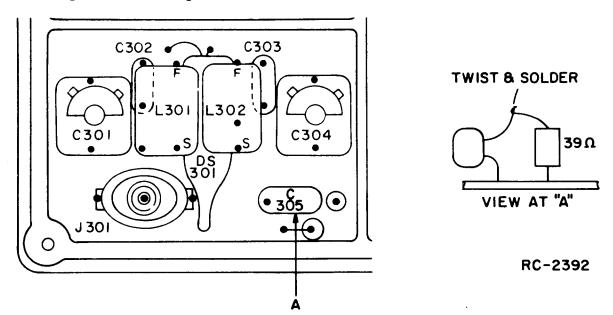


Figure 1 - Installation Diagram

TEST SPECIFICATIONS

1. Receiver specification changes are as follows:

20-dB Quieting0.6 microvolts12-dB SINAD0.4 microvoltsEIA Intermodulationunchanged (-70 dB)Critical Squelchless than 12-dB SINAD

2. More receiver sensitivity degradation can be obtained by increasing the value of the 39-ohm resistor in small increments.

MODIFICATION INSTRUCTIONS

REDUCTION OF INTERMODULATION INTERFERENCE (OPTION 8302)